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NAVAL POSTGRADUATE SCHOOL Monterey, California



THESIS

NATURAL CONVECTION COOLING OF A 3 BY 3 ARRAY OF RECTANGULAR PROTRUSIONS IN AN ENCLOSURE FILLED WITH DIELECTRIC LIQUID: EFFECTS OF BOUNDARY CONDITIONS AND COMPONENT ORIENTATION

by

Edgardo I. Torres

December 1988

Thesis Advisor:

Yogendra Joshi

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Natural Convection Cooling of a 3 by 3 Array of Rectangular Protrusions in an Enclosure Filled with Dielectric Liquid: Effects of Boundary Conditions and Component Orientation

by

Edgardo I. Torres LT, Columbian Navy B.S., Columbian Naval Academy, 1986

Submitted in partial fulfillment of the requirements for the degree of

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from the

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ABSTRACT

An experimental investigation of natural convection immersion cooling of two configurations of discrete heat sources in an enclosure filled with Fluorinert FC-75 has been conducted. A three by three array of rectangular protrusions was employed.

In the first study, using the same equipment set-up of Benedict [Ref. 13], the influence of changing the enclosure bottom surface boundary condition on flow patterns and heat transfer characteristics was examined. Both insulated and uniform temperature boundary conditions were considered.

In the second set of experiments, a new chamber with the protrusions oriented vertically was assembled and effects of component orientation on the heat transfer characteristics were examined. In addition, timewise variations of temperature in several locations were measured and interpreted at different power levels.

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TABLE OF SYMBOLS AND ABBREVIATIONS

Symbol	Description	Units
А	Area	m ²
α	Thermal diffusivity	m ² /sec
β	Volumetric expansion coefficient	1/K
cp	Specific heat	J/kg-°C
emf	Thermocouple voltage	volt
g	Acceleration of gravity	m/sec ²
Gr	Grashof number	Dimensionless
h	Heat transfer coefficient	W/m ² -°C
k	Thermal conductivity	W/m-°C
L	Characteristic length	m
L1	Component length in the vertical direction	m
L2	Summation of the ratios of the component fluid exposed areas to their perimeters	m
Nu	Nusselt number	Dimensionless
Nul	Nusselt number with length scale L1	Dimensionless
Nu2	Nusselt number with length scale L2	Dimensionless
ν	Kinematic viscosity	m ² /sec
ω	Uncertainty in the variables	Various

Power	Power dissipated by the heaters	W
Pr	Prandtl number	Dimensionless
Qconv	Energy added to the fluid	W
Qin	Energy input to the heaters	W
Q _{loss}	Energy loss by conduction	W
Qnet	Net power dissipated by the heater	W
Rc	Total thermal resistance	°C/W
Rp	Resistance of the precision resistor	ohms
Raf	Flux-based Rayleigh number	Dimensionless
Rat	Temperature-based Rayleigh number	Dimensionless
D	Density	kg/m ³
Tavg	Average of component temperature	°C
Tb	Back surface temperature of board	°C
Tc	Average heat exchanger temperature	°C
T _f	Average film temperature	°C
Ts	Back surface temperature of the	
	component	°C
Tsink	Average temperature of the heat	
	exchangers	
Vh	Voltage Across the Heaters	Volts
Vin	Input voltage	Volts
w	Chamber width	m
W	Unit of power	W

I. INTRODUCTION

A. STATEMENT OF THE PROBLEM

With the increase in circuit packaging density associated with the miniaturization of microelectronic components, heat dissipation has become a major problem in the design and construction of digital computers and high-power electronic equipment in general. Several alternatives to the solution of the problem have been studied in the past 10 years, including that of Chu [Ref. 1]. Among these, immersion cooling appears to be one of the most effective for achieving high heat-transfer coefficients.

B. IMMERSION COOLING: ANALYTICAL AND EXPERIMENTAL STUDIES

From the construction of the first electronic digital computer, the solution to the problem of heat dissipation from high packaging density electronic equipment has not been easy. Even though very interesting forced convection methods have been studied and very frequently used (Chu [Ref. 1] describes several methods of air- and water-forced convection cooling), the hardware that has to be added to supply the additional power and to store and circulate the cooling liquid can be cumbersome in any application.

The direct immersion of the electronic circuitry into dielectric liquids improves its cooling capability significantly. Baker [Ref. 2] found liquid cooling by free convection to be more than three times as

effective as free convective air cooling of the same device. He made heat transfer measurements from thin-film tantalum nitride resistors evaporated on Corning 7059 glass substrates. The substrates were 1.0 by 2.6 by 0.12 cm. All resistors were rectangular, with their height (dimension parallel to the flow) one-half their base. The surface areas of the resistors were 0.0106, 0.104, 0.477, and 2.00 cm². Two liquids were used in the study: freon with a Prandtl number of 3.9, and Dow Corning #200 silicone dielectric liquid with a Prandtl number of 126. The results showed that the heat transfer coefficient is approximately proportional to the cube root of the reciprocal of viscosity. It was also found that the convection coefficient does increase significantly as the source size decreases. The free convection heat transfer coefficient for the smallest source was more than an order of magnitude greater than for the largest source operated under the same conditions.

In a following study, Baker [Ref. 3] also examined different cooling techniques, such as nucleate boiling, forced convection, and bubble-induced mixing for cooling small heat sources.

Park and Bergles [Ref. 4] conducted experimental studies of natural convection from discrete flush-mounted rectangular heat sources on a circuit board substrate. Micro-electronic circuit elements were simulated with thin foil heaters supplied with DC power. Measurements were also made for protruding heaters of varying widths, in water and R-113. They found and documented the increase in heat transfer coefficient with decreasing width. This effect was greater in R-113 than in water. Also, for protruding heaters, the heat transfer

coefficients for the upper heaters in an array were found to be higher than those for the lower heaters. This behavior was not observed for flush-mounted heaters. As the distance between heaters increased, so did the heat transfer coefficients.

Chen, et al. [Ref. 5] made an experimental study of natural convection heat transfer in a liquid-filled rectangular enclosure with 10 protruding heaters from one vertical wall. The top surface of the enclosure maintained at a uniform temperature acted as the heat sink. All other surfaces, except the heater locations, were unheated. The enclosure was 16.7 cm in height, 2.3 cm in width, and 19.6 cm in depth (horizontal z-direction of the heaters). The 10 heaters were 0.8 cm high, 1.11 cm wide, and 19.6 cm deep. The vertical spacing between heaters was equal to the heater height. Distilled water and ethylene glycol were used as working fluids. Experimental results show that the bottom heater (heater 1), except for high Rayleigh number runs, has the highest heat transfer coefficient. The heat transfer coefficients at heaters 7, 8, and 9 are nearly the same and present the lowest values among the heaters. It was also shown that heat transfer coefficient decreases up to heater 7. At high Rayleigh numbers, the top heater (10) has the highest heat transfer coefficients. The flow visualization carried out indicates a core flow within the enclosure and a recirculating cell in the gap between heaters. Approximate measurements of the fluid velocity were provided from the particle traces in the flow visualization.

Keyhani, et al. [Ref. 6] experimentally studied the buoyancy-driven flow and heat transfer in a vertical cavity with discrete flush heat sources on one vertical wall while the other vertical wall was cooled at a constant temperature. This enclosure contained 11 alternatively unheated and flush-mounted rows of isoflux heated strips. The liquid was ethylene-glycol with a Prandtl number of 150.

To examine the flow structure, visualization experiments were conducted for several power inputs. Finely ground aluminum powder (5 to 20 microns in size) was used to visualize the flow. The observed flow for a power input of 10 watts was highly structured except for small regions near the end walls. A primary flow circulating from the hot wall to the cold wall, a secondary flow with the same sense of circulation as the primary flow, and a tertiary flow in the opposite direction of the secondary flow were observed in the photographs taken at this power level. At a higher power level of 40 watts, the flow pattern above the mid-height region of the cavity showed transition from laminar to turbulent flow along the surface with heaters. The downward flow along the cold wall was still laminar. For a fixed power input, the heat transfer coefficient generally decreased with increase in height (or heater number). The rate at which Nusselt number decreased with the increase in heater number was found to be a strong function of the heater location.

Kelleher, et al. [Ref. 7] and Lee, et al. [Ref. 8] studied experimentally and numerically the cooling by natural convection of a water-filled rectangular enclosure with a long heater protruding from one vertical

wall and conducted flow visualization and heat transfer measurements with the heater at three different elevations. They found the twodimensional flow to be dual-celled, consisting of a buoyancy-driven upper cell, in which the major part of the fluid motion takes place and which accounts for the majority of the convective heat transfer, and a shear-driven lower cell in which the fluid motion arises due to the viscous drag from the upper cell.

Liu, et al. [Ref. 9] used a three-dimensional finite difference method to study the natural convection cooling of an array of chips mounted on a vertical wall of a three-dimensional rectangular enclosure filled with a dielectric fluid Fluorinert FC 75. They found the long time solution to be oscillatory. Maximum chip temperatures were found on the top surfaces of the three top chips. However, these maximum temperatures did not all occur at the same time, but alternated among these three chips as time proceeded in a rather regular fashion. It was also observed that the bottom sink was quite ineffective in removing heat from the enclosure and that the convective circulation was essentially limited to the chip areas.

Joshi, et al. [Ref. 10] carried out an experimental investigation to study the natural convection cooling of a 3 by 3 array of heated protrusions in a rectangular enclosure filled with dielectric fluid FC-75. They observed that at low power levels (0.1 watts), the flow structure was largely determined by the thermal conditions at the enclosure surfaces. With increasing power levels (0.7 to 3.0 watts), an upward flow developed adjacent to each column of components. The flow away

from the elements became strongly three-dimensional and timedependent with increasing thermal inputs. Component surface temperatures were used to obtain a heat transfer correlation over the range of power levels examined.

Liu, et al. [Ref. 11] carried out a three-dimensional numerical study of immersion cooling of a chip array by laminar natural convection in a rectangular enclosure filled with a dielectric liquid. They determined the local temperature responses on the chip surfaces, their dynamic behaviors, and their dependence on the enclosure gap size. It was found that the temperature responses are decidedly oscillatory with wave forms ranging from simple to complex, and that maximum chip surface temperatures occur on the top row of chips for large gap sizes but oscillate among all three rows of chips for small gap sizes.

C. OBJECTIVES

The work reported here is a continuation of thesis research conducted at the Naval Postgraduate School by Pamuk [Ref. 12] and Benedict [Ref. 13]. The numerical studies by Liu, et al. [Ref. 9] and Liu, et al. [Ref. 11] were the motivation for some of the specific investigations carried out.

The objectives of the present investigation are twofold: The first is to examine the effect of bottom surface boundary condition on thermal transport in the natural convection cooling of a 3 by 3 array of horizontally arranged protruding elements on a vertical wall. The second objective is to examine heat transfer, fluid flow characteristics,

and the influence of the width of the chamber during the natural convection cooling of a 3 by 3 array of vertically arranged protruding elements on a vertical wall. Temperature fluctuation measurements were plotted and compared with existing numerical analysis of Liu, et al. [Refs. 9 and 11] and Benedict [Ref. 13]. For both studies, flow visualizations were also carried out.

II. EXPERIMENTAL SET-UP

A. GENERAL CONSIDERATIONS

Two different experimental configurations were used for the studies reported here. In the first, a 3 by 3 array of rectangular elements with the largest dimension aligned horizontally was examined. In the second study, the largest dimensions were in the vertical direction. The two experimental configurations are next described.

The details of the experimental procedures are available in Benedict [Ref. 13]. The Data Acquisition Programs were the same as used by Pamuk [Ref. 12] and Benedict [Ref. 13] with minor modifications in output format and number of channels. These programs are collected in Appendix D.

1. Experimental Set-Up for the Horizontal Arrangement

A schematic sketch of the arrangement is provided in Figure 2.1 (after Benedict [Ref. 13]). The configuration is the same as the one used by Joshi, et al. [Ref. 9] and Benedict [Ref. 13]. The distribution of the components and the top view of the chamber are illustrated in Figures 2.2 and 2.3 (both after Benedict [Ref. 13]).

This part of the thesis examines the effect of changing the enclosure bottom surface boundary condition on the overall thermal behavior of the system. A more detailed description of the experimental arrangement can be found in Benedict [Ref. 13].













2. Experimental Set-Up for the Vertical Arrangement

The chamber assembly, illustrated in Figure 2.4 was made of 19.05 mm plexiglass with dimensions of 241.13 mm length, 152.0 mm height, and 120.65 mm width. As in the first arrangement, the chamber was filled with FC-75, a dielectric fluid through tubing at the bottom of the chamber.

In both experimental configurations, two heat exchangers, one at the top and one at the bottom, were used (see Figure 2.1). The design of the exchangers for the first configuration is described in Joshi, et al. [Ref. 10]. In the second study, several modifications were made to reduce the heat transfer from the outside environment to the colder circulating water. The resulting design is seen in Figure 2.5. The external walls of both top and bottom heat exchangers were made of plexiglass. The walls acting as the top and bottom of the fluid-filled enclosure were aluminum plates 3 mm thick, chosen to provide an almost isothermal surface condition. Inlet and outlet headers were provided for flow distribution. Three thermocouples, symmetrically placed along the plate length, were used for the calculation of the average surface temperatures. The heat exchangers could be accessed easily to block one or more of the channels to reduce the coolant flow rates.

A 3 by 3 array of discrete protrusions, vertically arranged (see Figure 2.6), was mounted on a 19.05 mm thick plexiglass card. The card was slid into the chamber and was kept in location by plexiglass supports that prevented its linear movement as well as rotation.













Figure 2.6 Simulated Circuit Card for the Vertical Arrangement

The chamber design allowed the replacement of the card in a simple way. The upper heat exchanger could be removed and the new card could be easily installed. This permits the installation of different card configurations (staggered, flush mounted, etc.) in the future without much additional effort. By moving the card back or forth, the chamber width could be changed. This was done in order to study the effect of this parameter in the overall heat transfer.

The heated components in both studies were aluminum blocks of 8 mm by 24 mm and 6 mm high (see Figure 2.7–after Benedict [Ref. 13]). The dimensions and geometry simulate approximately a 20-pin dual-in-line-package. A nearly uniform heat flux condition was maintained at the base of each block by attaching a foil-type heater with a resistance of about 11 ohms. The foil heaters contained a network of Iconel foil mounted on a Kapton backing and were 23.6 mm by 7.6 mm in dimension and were bonded to the base of each aluminum block using a high thermal conductivity epoxy (Omega Bond 101).

Temperatures at the center of each fluid exposed component face were determined using .127 mm diameter copper-constantan thermocouples. Thermocouple locations on each heater are illustrated in Figure 2.7.

All the thermocouples were connected to an HP-3497 automatic data acquisition system controlled by an HP-9826 microcomputer. Power to the heaters was supplied by a 0-40 volt, 0-1A DC



Figure 2.7 Heating Element and Thermocouple Location

power supply. A simultaneous measurement of the overall voltage drop, along with the voltage drop across each heater, allowed the computation of the power dissipation through individual heaters.

Flow visualization was carried out with a 4 mw Helium-Neon laser for illumination. To produce a plane of light, a cylindrical lens was used (see Figure 2.8– after Benedict [Ref. 13]). The laser sheet illuminated magnesium particles (specific gravity of 1.74) that were added to the FC-75 (specific gravity of 1.76 at 25° C). This technique allowed for the visualization of a single two-dimensional plane of the flow field. Time exposure photographs of the flow were obtained using a Nikon F-3 camera with a 50 mm lens, a MD-4 motor drive, and a MT-2 intervalometer.


III. RESULTS AND DISCUSSIONS FOR HORIZONTAL ARRANGEMENT

A. FLOW PATTERNS

Flow visualization was carried out in six vertical planes, seen in Figure 3.1 (after Benedict [Ref. 13], for the two different bottom boundary conditions: 20° C and insulated. The three-dimensional transport responses, across the range of power dissipation of 0.1 W to 3.0 W, were inferred from these visualizations. In the following, a detailed description of the observed flows is provided.

1. Flow Patterns for the Bottom Boundary at 20° C

The flow patterns observed at several power dissipation levels from no dissipation to 3.0 W are collected in Figures 3.2 to 3.7. Visualization with no power (see Figures 3.2 and 3.3) was to examine the natural convection flow due only to the difference in temperature between the two heat exchangers, and its possible influence on the flow patterns, with the heaters turned on.

At no power, the flow consisted of a single clockwise cell that occupied the entire chamber. This overall flow was established as a result of the temperature differences between the enclosure walls. The three-dimensionality of the flow was evident from visualizations in the various planes.

At 0.1 W, the pattern observed at no power in Figures 3.2 and 3.3 was completely distorted and no remains of the strong clockwise





Figure 3.1 Top View of the Enclosure With the Card Placed in Position



Figure 3.2 Visualization With No Power in Planes 1 (a), 2 (b), and 3 (c)











Figure 3.5 Visualization With 1.1 W in Planes 4 (a), 5 (b), and 6 (c)









flow were seen. Joshi, et al. [Ref. 10] at the same power level reported two very well defined large clockwise cells, one on each side of the central component column. The present visualization showed that the flow now was completely dominated by the relatively high temperature of the bottom heat exchanger. The effects of the buoyancy forces due to the power dissipation were small except in plane 1 (close to the heaters), where there was a well defined upflow.

In plane 2, the particle traces showed a decrease in velocity. Also, dark regions, as observed in Joshi, et al. [Ref. 10], were seen. These were, however, thinner and not well defined. These nearly quiescent regions appear due to the stable stratification produced by the bottom heat exchanger. Descending fluid from the top is unable to penetrate the colder layer of fluid at the bottom. In plane 3, a downflow resulted due to an increase in the density of the colder fluid, in contact with the upper heat exchanger, at 10° C.

At 1.1 W (see Figure 3.4), a well defined pattern could be observed in planes 1 and 2. Along the central column of heaters, the upflow was wider and stronger than near the adjacent columns. This flow was the result of the interaction of an upflow along the central column, a clockwise flow around the right column (heaters 1, 2, and 3), and a counterclockwise flow around the left column (heaters 7, 8, and 9). In plane 3, a downflow of cold liquid was seen. In Figure 3.5, flow patterns at 1.1 W in planes 4, 5, and 6 are illustrated. It is possible in these pictures to appreciate in a side view the strong upflow adjacent to the components. The basic difference with the flow pattern found in the study by Joshi, et al. [Ref. 10] at the same power level is still that the inactive zone in the bottom of the chamber is not well defined.

With further increase in the power level, the flow in plane 1 exhibited stronger upflow near the components. The buoyancy forces generated by the power dissipation here were strong enough to extend their influence to planes 2 and 3. At 3.0 W, a very thin, dark layer was still observed at the bottom of the chamber (see Figure 3.6). A view of the flow patterns in planes 4, 5, and 6 is illustrated in Figure 3.7. This figure shows a buoyant fluid layer adjacent to the components. In the remaining chamber, the motion was completely random.

2. Flow Pattern With the Bottom Boundary Insulated

The flow pattern for this condition showed similar trends as discussed in section A.1. The induced flow due to the difference in temperature between the two heat exchangers was not appreciable.

B. HEAT TRANSFER MEASUREMENTS

Heat transfer measurements were made at power levels of 0.1, 0.7, 1.1, 1.5, and 3.0 watts for the two bottom surface boundary conditions. The temperature at the top heat exchanger was maintained constant at 10° C in all experiments. Temperature and flux-based Rayleigh numbers (Rat and Rat) were calculated in a manner identical to that discussed in Joshi, et al. [Ref. 10] and plotted versus Nusselt number (Nu1). These are defined in the Table of Symbols and Abbreviations.

1. Heat Transfer Measurements With the Bottom Boundary at 20° C

Component surface temperature measurements at various power levels are collected in Tables 1 through 8 in Appendix C. The nondimensional heat transfer parameters in the form of Nusselt versus Rayleigh numbers are illustrated in Figures 3.8 and 3.9. In the same plots, the correlations found by Joshi, et al. [Ref. 10] were also plotted.

We can see that having the bottom heat exchanger at 20° C results in general in lower Nusselt numbers than those found by Joshi, et al. [Ref. 10] in the range of Rayleigh numbers considered. At higher power levels, when the temperature of the heaters was considerably higher than the bulk temperature of the dielectric fluid, the difference in Nusselt numbers is smaller than at lower power levels. The Nusselt number at a flux-based Rayleigh number of 10⁶ found by Joshi, et al. [Ref. 10] was 20.4, while the Nusselt number obtained here for the same Rayleigh number was 19. At lower power levels 0.1 W and 0.7 W, the differences in Nusselt number were greater, and the decrease in the heat transfer coefficient was significant. The Nusselt number of 10⁶, while the Nusselt obtained with the present configuration was 2.9.

At power levels of 0.1 W and 0.7 W, a small increase in the upper heaters' temperatures over the lower ones was observed. At higher power levels, the highest temperatures were found irregularly in different components.



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Figure 3.9 Plot of Temperature-Based Rayleigh Number Versus Nusselt Number

The component that presented the largest variations from the mean in the heat transfer coefficients was the upper component in the central column (heater 6). This is evidenced as deviations from the general trend of the obtained data. The variations (lower heat transfer coefficient at low power levels, and higher heat transfer coefficients at higher power levels) are expected because this component receives the influence of the combined upflowing streams (produced by the other heaters), as was observed and documented in the flow visualization results in Section A.1. The effect is greater at higher power levels when the component's temperature is substantially larger than the bottom heat exchanger temperature.

2. Heat Transfer Measurements With the Bottom Boundary Insulated

The results of the temperature measurements with the bottom boundary insulated and the reduced dimensionless parameters are collected in Tables 9 through 16 in Appendix C. In Figures 3.10 and 3.11, flux and temperature Rayleigh numbers versus Nusselt numbers were plotted. Correlations found by Joshi, et al. [Ref. 10] were also plotted for comparison. It was seen that having the bottom heat exchanger insulated improved the cooling at low power levels (0.1 W and 0.7 W) over that obtained with the bottom boundary maintained at 20° C. This result is expected because now the temperature of the bottom boundary was 15° C at 0.1 W and 17° C at 0.7 W. At a power level of 3.0 W, no cooling improvement was observed. The temperature for the bottom boundary at 3.0 W was 22° C.







Comparisons with the correlation obtained by Joshi, et al. [Ref. 10] show a decrease in the heat transfer coefficient when the lower boundary was insulated. This was evidenced by the lower Nusselt numbers at all power levels.

IV. RESULTS AND DISCUSSIONS FOR VERTICAL ARRANGEMENT

A. FLOW VISUALIZATION

The visualization for this experiment was tried for a chamber width of 9 mm. As was expected, there was almost no flow in the narrow gap between components and the front wall. A boundary layer-like behavior was observed on the vertical side faces of the components. The photography process was complicated because the thickness of the plane to be illuminated by the laser sheet for this chamber width was only 3 mm.

B. HEAT TRANSFER MEASUREMENTS

Component surface temperature measurements were made for chamber widths of 30 mm and 9 mm (see Figure 4.1). The power level range was 0.1 W to 3.0 W. Temperatures of the top and bottom boundaries were maintained constant at 10° C. Plots of Nul versus Raf are provided for comparisons with data obtained by Benedict [Ref. 13].

1. Heat Transfer Measurement for w = 30 mm

Tables 17 through 28 in Appendix C compile component surface temperature and resulting nondimensional heat transfer data for this gap size with increasing power levels. The mean values of the component averaged temperatures over the nine heated components were 13° C for 0.1 W and 47° C for 3.0 W. In the range 0.1 W to 1.1 W, the lowest T_{avg} levels were on the bottom-row components



Figure 4.1 Side View Showing the Chamber Widths Used in the Experiment

(components 1, 4, and 7). The observed tendency was that temperatures on specific locations on the components in the top row were higher than those in the same location on the components in lower rows. As was pointed out by Liu, et al. [Ref. 11], the possible reason for this might be that components in the top row are in contact with warmer liquid, and the upper-row components are located in the heated wake regions of the lower rows. Additionally, the stratified fluid away from the components, which feeds fluid toward the component rows, is also at higher temperature for the upper rows.

Analyzing individual components in the middle and lower rows, for all power levels, the minimum measured temperatures were on the bottom surfaces. This trend is also supported by Liu, et al. [Ref. 9]. On the top row components, the lowest temperatures were on either one of the vertical side faces. Maximum temperatures were found generally on the component surface facing the front chamber wall. Liu, et al. [Ref. 11] obtained numerically maximum temperatures in the surfaces facing upward and attributed this to the fact that the heated flow coming off the vertical surfaces reduced the heat transfer coefficient at the component top surface. At higher power levels, oscillations in temperature changed the locations of the maximum and minimum instantaneous values, but the general tendencies found earlier were still noticed.

In Figure 4.2, a plot of Nul versus Ra_f is seen. Data obtained from Benedict [Ref. 13] is also plotted. A linear least squares fit to the present measurements in Figure 4.2 was performed. This is given by:



Figure 4.2 Comparison of the Nondimensional Heat Transfer Measurements for Two Different Component Orientations

Present measurements and curve fit are for the vertical arrangement.

Nul = 0.28
$$\operatorname{Ra}_{f}^{0.23}$$
 in the range 3 * 10⁸ < Ra_{f} < 10¹⁰
and 15 < Pr < 30.2 (4.1)

and the one obtained with the data from Benedict [Ref. 13] was:

Nul = 0.28
$$\text{Ra}_{\text{f}}^{0.22}$$
 in the range $10^7 < \text{Ra}_{\text{f}} < 2 * 10^8$
and $15 < \text{Pr} < 30.2$ (4.2)

Comparisons between Equations 4.1 and 4.2 indicate that Nu appears not to depend on the orientation of the components in the range of Ra_f and Pr considered. This is illustrated in Figure 4.2

2. Heat Transfer Measurement for w = 9 mm

In Tables 29 through 40 in Appendix C, component temperatures and resulting nondimensional heat transfer data are compiled. Decreasing the chamber width from 30 mm to 9 mm produced some increase in the average temperature of the components T_{avg} . This behavior was expected considering that now the surface of both top and bottom heat exchangers has been reduced to 30 percent of its former value. The mean value of the component averaged temperatures over the nine heaters for a power of 0.1 W was 14.5° C, 1.5° C higher than the average temperature obtained with 30 mm width. For a dissipation level of 3.0 W, the mean value of the components' averaged temperature over the nine heaters was 51° C, 4.0° C higher than the average observed for the 30 mm width. The T_{avg} value increased from the bottom to the top row, as was also found for w = 30 mm. Analyzing individual components on the bottom row (components 1, 4, and 7), minimum temperatures were found on the bottom surfaces.

Plots of Nul versus Ra_f are illustrated in Figure 4.3. The correlation obtained for this chamber width was:

Nul = 0.073
$$\operatorname{Ra}_{f}^{0.28}$$
 in the range 3 * 10⁸ < Ra_{f} < 10¹⁰
and 15 < Pr < 30.2 (4.3)

This correlation indicates the expected decrease in Nul for the same Ra_{f} , when compared with Equation 4.1 for w = 30 mm.

C. TEMPERATURE FLUCTUATIONS IN STEADY STATE

Oscillations in component surface temperatures following achievement of nominally steady conditions were measured in the dissipation range of 0.1 W to 3.0 W. Three thermocouples were scanned at a rate of approximately three times per second for a period of 200 seconds. Plots of surface temperature variations were made in order to display the long-time temperature fluctuations and compare with results of Liu, et al. [Ref. 11] and Benedict [Ref. 13]. Figure 4.4 is a vertical arrangement diagram which portrays the location of the scanned thermocouples.

1. Surface Temperature Fluctuations for a w = 30 mm

Temperature oscillations for this chamber width are illustrated in Figures 4.5 through 4.7. It was observed that at all power







Figure 4.4 Location of Thermocouples Scanned for Measurements of Fluctuations



Figure 4.5 Temperature Fluctuations for Thermocouple No. 0 at Different Power Levels



Figure 4.6 Temperature Fluctuations for Thermocouple No. 12 at Different Power Levels



Figure 4.7 Temperature Fluctuations for Thermocouple No. 31 at Different Power Levels

levels considered, there were no temperature fluctuations on the components in the lower row. Benedict [Ref. 13] documented with heat transfer measurement and flow visualizations that the stagnant fluid layer above the bottom heat exchanger prevented the penetration of warmer fluid, resulting in conduction-dominated transport for the bottom row of components.

At 0.1 W, a spread in temperature of less than 0.5° C was observed between the six thermocouples that were scanned. Increasing the power level to 0.7 W, oscillation amplitudes with a mean of 0.7° C were observed in component 6. At 1.1 W, the amplitude increased to 0.8° C. Benedict [Ref. 13] found that a component at the same relative location and power level in a horizontal arrangement had almost no oscillations. At 2.5 W, oscillations of about 1.6° C were found. At 3.0 W, oscillations rose to almost 1.7° C at the same location. Benedict [Ref. 13] found at 3.1 W for the equivalent thermocouple an amplitude of 0.85° C.

2. Surface Temperature Fluctuations for w = 9 mm

Plots of temperature oscillations are illustrated in Figures 4.8 through 4.10. At 0.1 W, no fluctuations were found in any of the thermocouples scanned. At 0.4 W, fluctuations of 0.3° C were observed in the top row components. No fluctuations were observed in the middle and bottom row components.

Increasing the power dissipation level to 0.7 W, no fluctuations were observed in either the middle or the bottom rows, but







Figure 4.9 Temperature Fluctuations for Thermocouple No. 12 at Different Power Levels



Figure 4.10 Temperature Fluctuations for Thermocouple No. 31 at Different Power Levels

fluctuations of 0.7° C were observed in the top row. At 1.1 W, fluctuations in the top-row components were about 0.9° C. No fluctuations were observed at the middle and bottom rows. At 1.5 W, fluctuations of 0.2° C appeared in the components in the middle row and reached values of 1.1° C in the top-row components. At 3.0 W, the highest power level utilized in the experiments, fluctuation amplitudes on the top-row components were recorded at 2.0° C. It is interesting to note that no significant increase in the amplitude of the fluctuations was observed when the chamber width was changed from 30 mm to 9 mm. Liu, et al. [Ref. 11] calculated temperature oscillations peak to valley of 8° C for the 9 mm chamber width. They attributed the increase in the oscillation amplitude to the fact that now the flow is highly confined.

V. RECOMMENDATIONS

The design of the present chamber can be improved in many ways to give more versatility in the following experiments. The recommended changes that can be made to software and hardware include:

- Placement of the blocks can be done by screwing or attaching them to the board in a different way to the one used until now, which is bonding the chips to the board with glue. This would allow the experimenter to change a defective heater or change the orientation of the chips for a different set of experiments, using the same board and the same equipment set-up.
- To avoid the flow of dielectric liquid to the back of the chamber through the gaps between the board and the chamber walls that can alter the heat transfer results or the flow visualization, a small diameter O-ring can be used. A groove should be engraved in the board to allow the O-ring installation.
- Temperature measurements within the fluid and on the board surfaces should also be performed.
- a Fast, Fourier Transform algorithm should be developed to perform frequency analysis on the surface temperature fluctuations data. In addition, improvements in the plotting programs can be made.
- With the present set-up, different combinations of heaters could be powered, row-wise or column-wise or staggered, instead of the entire array. This variation might help better to explain the heat transfer and flow characteristics of the chamber.

APPENDIX A

SAMPLE CALCULATIONS

A. CONVERSION OF THERMOCOUPLE VOLTAGES TO TEMPERATURES

(Channels 0 to 60 and 71 to 76, in the data acquisition system)

$$T = D1 + D2 * Emf + D3 * Emf2 + D4 * Emf3 + D5 * Emf4$$
$$+ D6 * Emf5 + D7 * Emf6 + D8 * Emf7$$

where D1 to D9 are the calibration coefficients of the Omega thermocouples and are: 0.10086091, 25727.9, -767345.8, 7802-5596, -9247486589, 6.98E11, -2.66E13, and 3.94E14.

Calculating the temperature found in the thermocouple connected to channel 0 at 1.1 W gives:

Emf = 0.995E-3 VT = 24.48° C

B. CALCULATION OF HEATER POWER

Channels 61 to 70 in the data acquisition system are used to measure the supply voltage (61) and voltage to the heaters.

Power = Emf * (Volt - Emf)/Rp

Calculating the power dissipated by the heater #3:

C. CALCULATION OF THE DIMENSIONLESS PARAMETERS

1. Calculation of the Block Faces Areas

Dimensions of the aluminum blocks are: length 24 mm, width 8 mm, and thickness 6 mm.

 $\begin{array}{l} A_{cen} = 24 \ mm * 8 \ mm = 192 \ mm^2 = 1.92E{\text -}4 \ m^2 \\ A_{lef} = 24 \ mm * 6 \ mm = 144 \ mm^2 = 1.44E{\text -}4 \ m^2 \\ A_{rig} = 24 \ mm * 6 \ mm = 144 \ mm^2 = 1.44E{\text -}4 \ m^2 \\ A_{top} = 6 \ mm * 8 \ mm = 144 \ mm^2 = 4.8E{\text -}5 \ m^2 \\ A_{bot} = 6 \ mm * 8 \ mm = 48 \ mm^2 = 4.8E{\text -}5 \ m^2 \\ A_{tot} = \Sigma A = 576 \ mm^2 = 5.76E{\text -}4 \ m^2 \\ T_{avg} = \Sigma(T(I) * A(I))/A_{tot} \end{array}$

Calculating for component 3 at 1.1 W:

 $T_{avg} = (27.67 * 1.92E-4 + 25.73 * 4.8E-5 + 26.08$ * 1.44E-4 + 26.69 * 4.8E5) /5.76E-4 $T_{avg} = 26.63^{\circ} C$
2. Calculation of the Temperatures at the Back of the Components

Due to problems in the placement of the thermocouples that measure the temperature at the heaters, these temperatures were calculated with a calibration curve for w = 30 mm from data obtained in Benedict [Ref. 13]. This calibration cannot be applied to the case where the width of the chamber is very small. In such a case, when w = 9 mm, a one-dimensional conduction analysis was applied to find the back temperature.

The best fit for the calibration points was:

T(K) = 14.003957 * Power + 14.517501

So, for 1.1 W,

 $T = 29.92^{\circ} C$

3. To Calculate the Conduction Losses Through the Circuit Card

$$\begin{split} Q_{\rm loss} &= \Delta T/{\rm Rc} = 1/N \ \Sigma(T({\rm I}) - {\rm Tb}({\rm J}))/{\rm Rc} \\ R_c &= L/kA \\ R_c &= 19.5{\rm E}{\rm -}3/(0.195 * 8{\rm E}{\rm -}3 * 24{\rm E}{\rm -}3) = 520.83 \ {\rm K}/{\rm W} \\ L &= 19.5{\rm E}{\rm -}3 \ {\rm m} \\ k &= 0.195 \ {\rm W}/{\rm m}.{\rm K} \ ({\rm plexiglass \ conductivity} \ [{\rm Ref. \ 14}]) \\ A &= (24{\rm E}{\rm -}3 * 8{\rm E}{\rm -}3) \ {\rm m}^2 = 1.92{\rm E}{\rm -}4 \ {\rm m}^2 \\ Q_{\rm loss} &= (29.92 - 17.31)/520.83 \\ &= 0.024 \ {\rm W} \end{split}$$

4. To Find the Average Sink Temperature

Channels 58, 59, and 60 in the bottom heat exchanger and channels 61, 72, and 73 in the top heat exchanger.

$$\begin{split} T_{\rm sink} &= 1/{\rm N} \; (\Sigma T_{\rm tc} + \Sigma T_{\rm bc}) \\ T_{\rm sink} &= (10.05 + 10.1 + 10.02 + 10.11 + 10.12 + 10.13)/6 \\ T_{\rm sink} &= 10.08^{\circ} \; {\rm C} \end{split}$$

To find the net power dissipated by the heater, Qnet:

 $Q_{net} = Power - Q_{loss}$

For 1.1 W and component 3:

 $Q_{net} = (1.1 - 0.024) W$ = 1.076 W

To find the convection coefficient h (from Newton's law of cooling):

 $\begin{aligned} & Q_{net} = h * A_{tot} * \Delta T \\ & \Delta T = T_{avg} - T_{sink} \\ & \Delta T = (26.63 - 10.08)^{\circ} C \\ & T = 16.55^{\circ} C \\ & h = Q_{net} / (A_{tot} * \Delta T) \end{aligned}$

5. For 1.1 W and Component 3

h = 1.09 / (16.55 * 5.76E-4) $h = 114.342 W/m^2 K$

6. To Calculate the Thermal Conductivity of the FC-75

 $k = (0.65 - 7.8947E-4 * T_{film})/10$

where $T_{film} = (T_{avg} + T_{sink})/2$.

At 1.1 W and chip 3:

T_{film} = (26.63 + 10.08)° C/2 T_{film} = 18.35° C k = 0.0645 W/m K

 To Calculate the Vertical Length Based Nusselt Number, Nu1

> Nul = h * L1/k Nul = 114.342 * 24E-3/0.0645 Nul = 42.54

 To Calculate the Ratio Area/Perimeter Based Nusselt Number, Nu2

 $L2 = \Sigma(A(i)/P(i))$ L2 = (24 * 8)/64 + (2 * 8 * 6)/(2 * 14) + (2 * 24 * 6)/(2 * 60) L2 = 11.229E-3 m L2 = 19.905

9. To Calculate the Density of the FC-75, ρ (Kg/m³)

 $\rho = (1.825 - 0.00246 * T_{film}) * 1000$

 $\rho = 1779.86 \text{ Kg}/\text{m}^3$

10. To Calculate the FC-75 Specific Heat, Cp (J/Kg K)

Cp = (.241111 + 3.7037E-4 * T_{film}) * 4180 Cp = 1036.25 J/Kg K

11. To Calculate the FC-75 Viscosity, $v(m^2/s)$

$$\begin{split} \nu &= (1.4074 - 2.964E\text{-}2 * T_{film} + 3.8018E\text{-}4 \\ &* T_{film}^2 - 2.7308E\text{-}6 * T_{film}^3 + 8.1679E\text{-}9 * T_{film}^4)\text{E}\text{-}6 \\ \nu &= .97557E\text{-}6 \text{ m}^2/\text{s} \end{split}$$

12. To Find the FC-75 Thermal Expansion Coefficient, $\beta(K^{-1})$

 $\beta = 0.00246/(1.825 - 0.00246 * T_{film})$

For 1.1 W and component 3:

 $\beta = 1.382\text{E-3 K}^{-1}$

13. To Calculate the FC-75 Thermal Diffusivity $\alpha(m^2/s)$

$$\alpha = k / \rho * Cp$$

For 1.1 W and component 3:

$$\alpha = 3.497 \text{E} \cdot 8 \text{ m}^2/\text{s}$$

14. To Calculate the Grashof Number

$$Gr = g * \beta * 1^3 * \Delta T/v^2$$

For 1.1 W and component 3:

15. To Calculate the Prandtl Number

$$Pr = v/\alpha$$
$$Pr = 27.89$$

16. To Find the Temperature Based Rayleigh Number

$$Ra = Gr * Pr$$

For 1.1 W and component 3:

Ra = 9.08E7

17. To Calculate the Flux Based Rayleigh Number

 $Ra_{f} = g * B * 1^{4} * Q_{net} / (k * v * \alpha * A_{tot})$ $Ra_{f} = 3.9E9$

APPENDIX B

UNCERTAINTY ANALYSIS

The uncertainty analysis was done using the method of Kline and McClintock, presented in Holman [Ref. 15]. The calculations will be done for the end values 0.1 W and 3.0 W, for a chamber width of 30 mm.

A. UNCERTAINTIES IN THE NET POWER ADDED TO THE FLUID

 $Q_{net} = Power - Q_{loss}$

Power = emf(I) * (Volt - emf(I))/Rp

Power = f(emf(I), Volt, Rp)

 $\frac{\partial \text{Power}}{\partial \text{emf(l)}} = \frac{\text{Volt} - 2 \cdot \text{emf(l)}}{\text{Rp}}$

 $\frac{\partial \text{Power}}{\partial \text{Volt}} = \frac{\text{emf(I)}}{\text{Rp}}$

$$\frac{\partial \text{Power}}{\partial \text{Rp}} = -\frac{\text{emf}(I) \cdot (\text{Volt} - \text{emf}(I))}{\text{Rp}^2}$$

$$W_{\text{power}} = \left[\left(\frac{\partial_{\text{power}}}{\partial_{\text{emf}(1)}} \right)^2 W_{\text{emf}(1)}^2 + \left(\frac{\partial_{\text{power}}}{\partial_{\text{volt}}} \right)^2 W_{\text{volt}}^2 + \left(\frac{\partial_{\text{power}}}{\partial_{\text{Rp}}} \right)^2 W_{\text{Rp}}^2 \right]^{\frac{1}{2}}$$

$$W_{\rm emf} = 0.001 \, {\rm V}$$

(by Resolution in the reading and precision of measuring devices)

 $W_{\rm Volt} = 0.001 \ {\rm V}$

(by Resolution in the reading and precision of measuring devices)

 $W_{\rm Rp} = 0.05 \ \Omega$

(including the added resistances)

For 0.1 W and chip 3:

emf(I) = 1.022 V

Volt = 1.225 V

 $Rp = 2.06 \Omega$

(measured resistance including resistances in the junctions, etc.)

 $\frac{\partial Power}{\partial emf(l)} = -0.397$

 $\frac{\partial \text{Power}}{\partial \text{Volt}} = 0.496$

 $\frac{\partial \text{Power}}{\partial \text{Rp}} = -0.0488$

 $W_{\text{power}} = \left[\left(-0.397 \right)^2 \cdot \left(0.001 \right)^2 + \left(0.496 \right)^2 \cdot \left(0.001 \right)^2 + \left(-0.0488 \right)^2 \cdot \left(0.05 \right)^2 \right]^{\frac{1}{2}}$

$$W_{power} = 0.00252 \text{ W}$$

$$\frac{W_{\text{power}}}{\text{Power}} = \frac{0.00252 \,\text{W}}{0.1 \,\text{W}} = 2.5 \,\%$$

$$Q_{loss} = \frac{\Delta T}{Rc}$$

where ΔT is the difference in temperature between the back surface of the chip and the back of the board.

$$Q = f(\Delta T, Rc)$$

$$\frac{\partial Q_{\text{loss}}}{\partial \Delta T} = \frac{1}{Rc} = \frac{Q_{\text{loss}}}{\partial Rc} = \frac{\Delta T}{Rc^2}$$

For 0.1 W and component 3:

$$\frac{\partial Q_{\text{loss}}}{\partial \Delta T} = \frac{1}{520.83 \text{ K/W}} = 0.00192$$

$$\frac{\partial Q_{\text{loss}}}{\partial \text{Rc}} = -\frac{0.12^{\circ}\text{K}}{(520.83)^2} = -4.424 \times 10^{-7}$$

$$WQ_{loss} = \left[\left(\frac{l}{Rc} \right)^2 W_{\Delta T} + \left(\frac{-\Delta T}{Rc^2} \right) W_{Rc} \right]$$

$$W_{\Delta T} = 10\% = 0.012^{\circ} \text{ C}$$

$$W_{\rm Rc} = 10\% = 52.083 \text{ K/W}$$

$$WQ_{loss} = \left[(0.00192^2 \cdot 0.012^2 + (-4.424 \times 10^{-7})^2 \cdot (52.083)^2 \right]^{\frac{7}{2}}$$

$$WQ_{loss} = (5.352 \times 10^{-10})^{\frac{1}{2}} = 3.258E-5$$

$$\frac{WQ_{loss}}{Q_{loss}} = 0.14 = 14\%^{1}$$

$$WQ_{\text{net}} = \left[\left(W_{\text{power}} \right)^2 + \left(WQ_{\text{loss}} \right)^2 \right]^{\frac{1}{2}}$$

$$WQ_{\text{net}} = \left[(0.00252)^2 + (3.258 \times 10^{-5})^2 \right]^{\frac{1}{2}}$$

$$WQ_{net} = \pm 0.025 W$$

$$\frac{WQ_{net}}{Q_{net}} = \pm 2.5\%$$

¹The uncertainties in the losses are relatively big, but they do not have a large effect on the final undertaking.

For 3.0 W and component 3:

e

$$emf(I) = 5.647 V$$

$$Volt = 6.762$$

$$Rp = 2.06\Omega$$

$$\frac{\partial Power}{\partial emf(I)} = -2.2$$

$$\frac{\partial Power}{\partial Volt} = 2.74$$

$$\frac{\partial \text{Power}}{\partial \text{Rp}} = 1.484$$

$$W_{\text{power}} = \left[(-2.2)^2 \cdot (0.00)^2 + (2.74)^2 \cdot (0.00)^2 + (1.484)^2 \cdot (0.05)^2 \right]^{\frac{1}{2}}$$

$$W_{\text{power}} = 0.74 \text{ W}$$

$$\frac{W_{\text{power}}}{\text{power}} = \frac{0.074}{3.0} = \pm 2.5\%$$

$$\frac{\partial Q_{\text{loss}}}{\partial \Delta T} = \frac{1}{520.83} \text{k/w} = 0.00192$$

$$\frac{\partial Q_{\text{loss}}}{\partial Rc} = -\frac{21.68}{(520.83)^2} = -7.993E - 5$$

$$WQ_{1_{0}} = \left[(0.00192^{\circ} \cdot (2.168)^{\circ} + (-7.992E - 5)^{\circ} \cdot (52.083)^{\circ} \right]^{2}$$

 $WQ_{loss} = 0.059 W$

$$\frac{WQ_{loss}}{Q_{loss}} = 14.14\%$$

$$WQnet = \left[\left(W_{power} \right)^{2} + \left(WQ_{loss} \right)^{2} \right]^{2}$$

$$WQnet = \left[(0.074)^2 + (0.0059)^2 \right]^{\frac{1}{2}}$$

$$WQ_{net} = \pm 0.0742 W$$

$$\frac{WQ_{net}}{Q_{net}} = \pm 2.5\%$$

B. UNCERTAINTY IN RAYLEIGH AND NUSSELT NUMBERS Starting with:

$$Q_{net} = hA_{tot} (T_{avg} - T_{sink})$$

$$h = \frac{Q_{net}}{A_{tot} (T_{avg} - T_{sin k})}$$

$$h = f(Q_{net}, A_{tot}, \Delta T)$$

$$\frac{\partial h}{\partial Q_{net}} = \frac{1}{A_{tot}(\Delta T)}$$
$$\frac{\partial h}{\partial A_{tot}} = \frac{Q_{net}}{A_{tot}(\Delta T)^2}$$
$$\frac{\partial h}{\partial \Delta T} = \frac{Q_{net}}{A_{tot}(\Delta T)^2}$$

for 0.1 W and component 3:

$$A_{tot} = 5.76 \times 10^{-4} m^2$$
 (for all components)

$$\frac{\partial h}{\partial Q_{\text{net}}} = \frac{1}{(5.76 \times 10^{-4})(3.02)} = 574.87$$

$$\frac{\partial h}{\partial A_{tot}} = \frac{0.1}{(5.76 \times 10^{-4})(3.02)} = -99804.03$$

$$\frac{\partial h}{\partial \Delta T} = -\frac{-0.1}{\left(5.76 \times 10^{-4}\right) \left(3.02\right)^2} = -19.035$$

$$Wh = \left[\left(\frac{\partial h}{\partial Q_{net}} \right)^2 W Q_{net}^2 + \left(\frac{\partial h}{\partial \Delta_{tot}} \right)^2 W_{\Lambda_{tot}}^2 + \left(\frac{\partial h}{\partial \Delta T} \right)^2 W_{\Lambda T}^2 \right]^2$$

 $WQ_{net} = \pm 0.0025 W$

$$W_{\rm L} = \pm 10^{-5} \, {\rm m}$$

$$W_{\rm A} = \left[\left(10^{-5} \right)^2 + \left(10^{-5} \right)^2 \right]^{\frac{1}{2}} = 1.4 \, \text{IE} - 5 \, \text{m}^2$$

 $W_{\Delta T} = \pm 1\% = 0.03^{\circ} \text{ C}$

 $W_{\rm h} = \left[\left(574.87\right)^2 \cdot \left(0.0025\right)^2 + \left(99804\right)^2 \cdot \left(1.4\,\,\mathrm{IE}-5\right)^2 + \left(19.035\right)^2 \cdot \left(0.03\right)^2 \right]^{\frac{1}{2}}$

$$W_{\rm h} = (2.065 + 0.019 + .3260)^{\frac{1}{2}}$$

$$= \pm 2.09 \text{ W/m}^2 \text{ K}$$

$$\frac{W_{\rm h}}{\rm h} = \frac{2.09}{57.487} = \pm 3.64\%$$

For 3.0 W and component 3:

$$\frac{\partial h}{\partial Q_{net}} = \frac{1}{(5.76 \times 10^{-4})(38.38)} = 45.52$$

$$\frac{\partial h}{\partial Q_{net}} = \frac{3.0}{2} = 235597.8$$

$$\frac{\partial \Pi}{\partial A_{\text{tot}}} = \frac{3.0}{\left(5.76 \times 10^{-4}\right)^2 (38.38)} = 235597.84$$

$$\frac{\partial h}{\partial \Delta T} = \frac{3.0}{(5.76 \times 10^{-4})(38.38)^2} = 3,536$$

$$W_{\rm h} = \left[\left(45.52\right)^2 \cdot \left(0.0742\right)^2 + \left(235597.8\right)^2 \cdot \left(1.4\,{\rm IE}-5\right)^2 + \left(3.54\right)^2 \cdot \left(.38\right)^2 \right]^2 \right]^2$$

$$W_{\rm h} = \pm 4.92 \text{ w/m}^2 \text{ K}$$

$$\frac{W_{\rm h}}{\rm h} = \frac{4.92}{135.7} = 3.63\%$$

To find the uncertainty of Nusselt Number:

$$Nu = \frac{h_L}{k}$$

Nu = f(h, L, k)

 $\frac{\partial Nu}{\partial h} = \frac{L}{k}$ $\frac{\partial Nu}{\partial L} = \frac{h}{k}$

$$\frac{\partial Nu}{\partial k} = -\frac{hL}{k^2}$$

Since the thermal properties of the FC-75 (dielectric liquid) are values that depend on film temperatures, it is considered that there are no uncertainties in these values.

$$K = (0.65 - 7.89474E - 4 \cdot T_{film})/10$$

$$T_{film} = \frac{T_{avg} + T_{sin k}}{2}$$

For 0.1 W and component 3:

$$K = 0.064 \frac{W}{m K}$$

$$T_{film} = 11.51^{\circ} C$$

$$\frac{\partial Nu}{\partial k} = \frac{24 \times 10^{-3} m}{0.064 \text{ w/m K}} = 0.374$$

$$\frac{\partial Nu}{\partial k} = \frac{57.487}{24 \times 10^{-3}} = 2395.29$$

$$\frac{\partial Nu}{\partial k} = \frac{57.487 \times 24 \times 10^{-3}}{(0.064)^2} = 336.84$$

$$WNu = \left[\left(\frac{\partial Nu}{\partial h} \right)^2 Wh^2 + \left(\frac{\partial Nu}{\partial L} \right)^2 W_L^2 + \left(\frac{\partial Nu}{\partial k} \right)^2 Wk^2 \right]^{\frac{1}{2}}$$
$$WNu = \left[\left(0.374 \right)^2 \cdot \left(2.09 \right)^2 + \left(2395.29 \right)^2 \cdot \left(10^{-5} \right)^2 \right]^{\frac{1}{2}}$$

WNu = ±0.78

$$\frac{WNu}{Nu} = \frac{0.78}{21.55} = 0.036 = 3.6\%$$

For 3.0 W and component 3:

$$k_{f} = 0.0627 \frac{W}{mk}$$

$$T_{film} = 29.2^{\circ} C$$

$$\frac{\partial Nu}{\partial h} = \frac{24 \times 10^{-3} m}{0.0627} = 0.382$$

$$\frac{\partial Nu}{\partial L} = \frac{135.7}{24 \times 10^{-3}} = 5654.16$$

$$WNu = \left[(0.382)^2 \cdot (4.92)^2 + (5654.16)^2 \cdot (10^{-5})^2 \right]^{\frac{1}{2}}$$

$$WNu = \pm 1.88$$

$$\frac{WNu}{Nu} = \frac{1.88}{51.94} = 3.62\%$$

$$Ra_{f} = Gr_{f} \cdot Pr$$

$$Gr_{f} = \frac{g\beta L^{4}Q_{net}}{k_{f}v^{2}A_{tot}}$$

$$\Pr = \frac{V}{\alpha}$$

$$Gr_{f} = f(g,\beta,L^{4},Q_{net},k_{f},v^{2},A_{tot})$$

Consider fluid properties without uncertainties.

$$\frac{\partial \mathrm{Gr}_{\mathrm{f}}}{\partial \mathrm{L}^{4}} = \frac{g\beta Q_{\mathrm{net}}}{k_{\mathrm{f}} v^{2} \mathrm{A}_{\mathrm{tot}}}$$
$$\frac{\partial \mathrm{Gr}_{\mathrm{f}}}{\partial Q_{\mathrm{net}}} = \frac{g\beta \mathrm{L}^{4}}{k_{\mathrm{f}} v^{2} \mathrm{A}_{\mathrm{tot}}}$$
$$\frac{\partial \mathrm{Gr}_{\mathrm{f}}}{\partial \mathrm{A}_{\mathrm{tot}}} = \frac{g\beta \mathrm{L}^{4} Q_{\mathrm{net}}}{k_{\mathrm{f}} v^{2} \mathrm{A}_{\mathrm{tot}}}$$

For 0.1 W and component 3:

$$\beta = 0.00137 \text{ K}^{-1}$$

$$k_{f} = 0.064 \frac{W}{m.k}$$

$$r = 1.11259E - 6 \frac{m^{2}}{s}$$

$$\frac{\partial Gr_{f}}{\partial L^{4}} = 2.94E13$$

$$\frac{\partial \mathrm{Gr}_{\mathrm{f}}}{\partial \mathrm{Q}_{\mathrm{net}}} = 9.76\mathrm{E7}$$

$$\frac{\partial \operatorname{Gr}_{\mathrm{f}}}{\partial \mathrm{A}_{\mathrm{tot}}} = -1.69 \mathrm{E10}$$

$$WGr_{f} = \left[\left(\frac{\partial Gr_{f}}{\partial L^{4}} \right)^{2} W^{2} L^{4} + \left(\frac{\partial Gr_{f}}{\partial Q_{net}} \right)^{2} W^{2} Q_{net} + \left(\frac{\partial Gr_{f}}{\partial A_{tot}} \right)^{2} WA_{tot} \right]^{\frac{1}{2}}$$

WGr_f =
$$\begin{bmatrix} (2.94 \pm 1.3)^2 \cdot (5.5 \pm -1.0)^2 + (9.76 \pm 7)^2 \cdot (0.0025)^2 \end{bmatrix}^{\frac{1}{2}} + (1.69 \pm 1.0)^2 \cdot (4.8 \pm -7)^2$$

$$WGr_{f} = [2.6E8 + 5.9536E10 + 6.5E7]^{2}$$

$$W_{Grf} = \pm 243569$$

$$\frac{W_{\rm Gr_f}}{\rm Gr_f} = \frac{243569}{9.67\rm E6} = 2.5\%$$

$$W_{Raf} = 2.5\%$$

For 3.0 W and component 3:

$$\beta = 0.014 \text{ K}^{-1}$$

$$v = 0.80402 \times 10^{-6} \frac{m^2}{s}$$

$$k_f = 0.0627 \ \frac{W}{m.K}$$

$$\frac{\partial \mathrm{Gr}_{\mathrm{f}}}{\partial \mathrm{L}^{4}} = 17.6\mathrm{E15}$$

$$\frac{\partial \mathrm{Gr}_{\mathrm{f}}}{\partial \mathrm{Q}_{\mathrm{net}}} = 19.5\mathrm{E7}$$

$$\frac{\partial Gr_f}{\partial A_{tot}} = 1.0E12$$

$$WGr_{f} = \left[(17.6E15)^{2} \cdot (5.5E-10)^{2} + (19.5E7)^{2} \cdot (0.0742)^{2} + (1.0E12)^{2} \cdot (4.8E-7)^{2} \right]^{2}$$

$$WGr_{f} = [9.3E13 + 2.09E14 + 2.38E11]^{3}$$

$$\frac{WGr_{\rm f}}{Gr_{\rm f}} = \frac{17405183}{584920180} = 2.9\%$$

$$W_{Raf} = 2.9\%$$

APPENDIX C

TABLES

TABLE 1

TEMPERATURE DATA FOR INPUT POWER 0.1 W BOTTOM BOUNDARY AT 20° C

RESULTS ARE STORED IN FILE: 08021455

AMBIENT TEMP : 24.3 C VOLTMETER READING : 1.025 V HEAT EXCHANGER TEMP.: 10-20 C

ALL TEMPERATURES ARE IN DEGREES CELCIUS

		CENTER	TOP	RIGHT	LEFT	BOTTOM	BACK
CHIF	NO1: POWER	17.46E+00 (WATTS):	17.48E+00 10.01E-02	17.48E+00	17.47E+00	17.54E+00	18.04E+00
CHIF	NO2: POWER	17.40E+00 (WATIS):	17.44E+00 10.00E-02	17.47E+00	17.41E+00	17.47E+00	17.36E+00
CHIP	NU3# POWER	17+13E+00 (WATTS):	17.08E+00 99.84E-03	17.16E+00	17.22E+00	17.29E+00	17.61E+00
CHIP	NO4: POWER	17.57E+00 (WATTS):	17.56E+00 98.84E-03	17.44E+00	15.60E+00	17.48E+00	17.89E+00
CHIF	NO5: POWER	17.48E+00 (WATTS):	17.62E+00 99.24E-03	17.56E+00	17.51E+00	17.58E+00	17.92E+00
CHIP	NO6: POWER	22.68E+00 (WATTS):	17.39E+00 99.12E-03	17.43E+00	17.38E+00	17.55E+00	18.42E+00
'IP	NO7: POWER	17.59E+00 (WATTS):	17.62E+00 10.04E-02	17.60E+00	17.55E+00	17.74E+00	18.32E+00
CHIP	NO8: POWER	17.58E+00 (WATTS):	17.64E+00 10.07E-02	17.67E+00	17.58E+00	17.60E+00	18.47E+00
CHIP	N09: POWER	17.33E+00 (WATTS);	17.15E+00 99.32E-03	17.34E+00	17.30E+00	17.36E+00	17.82E+00

AVERAGE HEAT EXCHANGERS TEMPERATURES: BOTICM: 10.01E+00 TOP: 19.97E+00

BACK PLANE TEMPERATURES ARE :

T(55):	17.81E+00
T(56):	18.09E+00
T(57):	17.54E+00
T(72):	18.33E+00
T(73):	18.43E+00
T(74):	18.91E+00
T(75):	18.07E+00
T(76):	18.40E+00
T(77):	18.29E+00

TEMPERATURE DATA FOR INPUT POWER 0.7 W BOTTOM BOUNDARY AT 20° C

RESULTS ARE STORED IN FILE: 08021717

AMBIENT TEMP : 24.4 C VOLTMETER READING : 3.218 V HEAT EXCHANGER TEMP.: 10-20 C

ALL TEMPERATURES ARE IN DECREES CELCIUS

	CENTER	TOP	RIGHT	LEFT	BOTTOM	BACK
CHIP HO1: POWER	24.74E+00 (WATTS):	24.02E+00 70.97E-02	23.96E+00	24.00E+00	24.09E+00	27.01E+00
CHIP NO2: POWER	24.71E+00 (WATTS):	23,81E+00 70,93E-02	23.96E+00	23.54E+00	23.80E+00	26.56E+00
CHIP NO3: POWER	23.83E+00 (WATTS);	23.69E+00 70.79E-02	23.59E+00	23.55E+00	23.60E+00	25.11E+00
CHIP NO4: POWER	24.30E+00 (WATTS):	23.71E+00 70.09E-02	23.60E+00	20.65E+00	23.60E+00	25.74E+00
CHIP NO5: POWER	24.26E+00 (WATTS):	23.46E+00 70.38E-02	23.44E+00	23.37E+00	23.69E+00	25.46E+00
CHIP NO5: POWER	26.78E+00 (WATTS):	24.05E+00 70.26E-02	23.44E+00	23.51E+00	24.08E+00	27.57E+00
'IP NO7: POWER	24.96E+00 (WATTS):	24.47E+00 71.19E-02	24.02E+00	23.81E+00	24.14E+00	27.58E+00
CHIP NO8: POWER	24.27E+00 (WATTS):	24.14E+00 71.40E-02	24.07E+00	23.85E+00	23.79E+00	29,43E+00
CHIP NO9: FOWER	23.90E+00 (WATTS):	23.70E+00 70.84E-02	23.62E+00	23.50E+00	23.44E+00	26.70E+00

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AVERAGE HEAT EXCHANGERS TEMPERATURES: BOITOM: 10.00E+00 TOP: 20.00E+00

BACK PLANE TEMPERATURES ARE :

T(55):	20.83E+00
T(56):	21.22E+00
T(57):	20.72E+00
T(72):	21.38E+00
T(73):	21.10E+00
T(74):	21.50E+00
T(75):	21.03E+00
T(76):	21.18E+00
1(77) *	21.23E+00

TEMPERATURE DATA FOR INPUT POWER 1.5 W BOTTOM BOUNDARY AT 20° C

RESULTS ARE STORED IN FILE: 08030205

AMBIENT TEMP : 24.4 C VOLTMETER READING : 4.7082 V HEAT EXCHANGER TEMP.: 10-20 C

ALL TEMPERATURES ARE IN DEGREES CELCIUS

	CENTER	TOP	RIGHT	LEFT	BOTTOM	BACK
CHIP NO1: POWER	33.28E+00 (WATTS):	31.29E+00 15.17E-01	31.67E+00	31.63E+00	31.81E+00	37.53E+00
CHIP NO2: POWER	33.22E+00 (WAITS):	31.21E+00 15.16E-01	31.50E+00	30.68E+00	31.25E+00	36.83E+00
CHIP NO3: POWER	31.23E+00 (WATTS):	31.26E+00 15.13E-01	30.99E+00	30.76E+00	30.63E+00	34.16E+00
CHIP NO4: POWER	33.06E+00 (WATTS):	31.52E+00 14.98E~01	31.54E+00	27.88E+00	31.60E+00	35.83E+00
CHIP NOS: POWER	32.56E+00 (WATTS):	30.25E+00 15.04E-01	30.60E+00	30.44E+00	31.30E+00	34.65E+00
CHIP NO6: POWER	20.87E+00 (WATTS):	32.79E+00 15.01E-01	30.75E+00	31.13E+00	32.43E+00	43.50E+00
P NO7: POWER	30.79E+00 (WATTS):	32.54E+00 15.21E-01	31.83E+00	31.29E+00	31.97E+00	38.83E+00
CHIP NO8: POWER	32.46E+00 (WATTS):	31.64E+00 15.26E-01	31.72E+00	31.46E+00	31.25E+00	43.11E+00
CHIP NO9: POWER	31.47E+00 (WATTS):	31.25E+00 15.14E-01	31.12E+00	30.80E+00	31.01E+00	37.41E+00

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AVERAGE HEAT EXCHANGERS TEMPERATURES: BOTTOM: 10.09E+00 TOP: 20.04E+00

BACK PLANE TEMPERATURES ARE :

T(55):	23.97E+00
T(56):	24.51E+00
T(57):	25.06E+00
T(72):	24.93E+00
T(73):	24.57E+00
T(74):	24.85E+00
T(75):	25.10E+00
T(76):	24.49E+00
T(77):	24.61E+00

TEMPERATURE DATA FOR INPUT POWER 3.0 W BOTTOM BOUNDARY AT 20° C

RESULTS ARE STORED IN FILE: 08041705

AMBIENT TEMP : 24.5 C VOLTMETER READING : 6.601 V HEAT EXCHANGER TEMP.: 10-20 C

ALL TEMPERATURES ARE IN DEGREES CELCIUS

	CENTER	TOP	RIGHT	LEFT	BOTTOM	BACK
CHIP NOI: POWER	49.47E+00 (WATTS):	45.65E+00 29.74E-01	46.44E+00	46.13E+00	45.76E+00	56.26E+00
CHIP NO2: POWER	48.99E+00 (WAITS):	45.37E+00 29.73E-01	46.33E+00	44.51E+00	46.02E+00	56.02E+00
CHIP NO3: POWER	44.62E+00 (WAITS):	45.57E+00 29.68E-01	45.04E+00	44.58E+00	44.60E+00	51.20E+00
CHIP NO4: POWER	49.59E+00 (WATTS):	46.17E+00 29.38E-01	46.77E+00	42.62E+00	46.97E+00	54.89E+00
CHIP NO5: POWER	48.69E+00 (WATIS):	43.92E+00 29.51E-01	45.19E+00	44.75E+00	46.43E+00	52.53E+00
CHIP NOG: POWER	37.80E+00 (WATTS):	48.64E+00 29.40E-01	45.04E+00	45.78E+00	47.85E+00	68.62E+00
'IP NO7: POWER	51.18E+00 (WATTS):	48.27E+00 29.82E-01	47.48E+00	46.51E+00	47.28E+00	58.60E+00
CHIP NO8: POWER	48.09E+00 (WATTS);	47.05E+00 29.91E-01	47.09E+00	46.58E+90	45.99E+00	67.94E+00
CHIP NO9: POWER	44.97E+00 (WATTS):	45.78E+00 29.63E-01	45.57E+00	45.11E+00	44.78E+00	58.25E+00
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AVERAGE HEAT	EXCHANGERS	TEMPERATURES:
BOTTOM:		10.98E+00
TOP:		20.08E+00

BACK PLANE TEMPERATURES ARE :

1(55):	31.46E+00
T(56):	32.62E+00
T(57):	34.30E+00
T(72):	33.38E+00
T(73):	32.78E+00
T(74):	33.27E+00
T(75):	33.99E+00
T(76):	32.43E+00
T(77):	32.42E+00

REDUCED DATA FOR INPUT POWER 0.1 W BOTTOM BOUNDARY AT 20° C

THE RAW EMF DATA ARE FROM THE FILE: 08021455 THE PONER SETTING PER CHIP WAS: 0.1 W

- CHIP
 ONET(H)
 Tavg-Ts
 Nu
 ZUNC IN Nu

 1
 99.93E-03
 74.63E-01
 29.10E-01
 13.42E-01

 1
 FEMPERATURE BASED RAYLEIGH NUMBER + E-7 IS:
 139.72E-03
 2.463E-01

 2
 UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS:
 134.16E-02

 FLUX BASED RAYLEIGH NUMBER + E-8
 135.26-04

 2
 UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS:
 458.54E-05
- 2 99.94E-03 74.15E-01 29.26E-01 13.50E-01 TEMPERATURE BASED RAYLEIGH NUMBER * E-7 IS: 138.74E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 135.03E-02 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 405.97E-04 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 458.97E-05
- 99.54E-03 71.59E-01 30.24E-01 13.99E-01
 TEHFERATURE BASED RAYLEIGH NUHBER ↓ E-7 IS: 13.57E-03
 WORGRIAINT IN THE TEMPERATURE BASED RAYLEIGH NUHBER IS: 139.86E-02
 FLUX EASED RAYLEICH NUMBER ↓ E-8 IS: 403.37E-04
 WORGRIAINT IN FLUX BASED RAYLEIGH NUMBER IS: 459.86E-05
- 4 98.64E-03 70.22E-01 30.52E-01 14.26E-01 TEMPERATURE BASED RAYLEIGH NUMBER * E-7 IS: 130.83E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS :142.58E-02 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 399.28E-04 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 464.52E-05
- 5 99.04c-03 75.15E-01 28.64E-01 13.32E-01 TEMPERATURE BASED RATLEIGH NUMBER * E-7 IS: 140.78E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 133.23E-02 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 403.22E-04 % UNCERTAINTY IN FLUX BASED RAYLFIGH NUMBER IS: 452.64E-05
- 5 98.92E-03 91.51E-01 23.49E-01 10.93E-01 TEMPERATURE BASED RATLEIGH NUMBER * E-7 IS: 174.75E-03 Z UNCERTAINTY IN THE TEMPERATURE BASED RATLEIGH NUMBER IS: 109.29E-02 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 410.50E-04 Z UNCERTAINTY IN FLUX BASED RATLEIGH NUMBER IS: 453.23E-05
- 7 10.02E-02 75.95E-01 28.72E-01 132.02E-01 TEMPERATURE BASED RAYLEIGH NUMBER + E-7 IS: 142.19E-03 % UNCCRIAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS :132.01E-02 FLUX BASED RAYLEIGH NUMBER 15= 15: 408.40E-04 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 457.14E-05
- 8 10.05E-02 75.98E-01 28.75E-01 13.18E-01 TEMPERATURE BASED RATLEIGH NUMBER * E-7 15: 142.45E-03 % UNCERIAINTY IN THE TEMPERATURE BASED RATLEIGH NUMBER IS :131.78E-02 FLUX BASED RAYLEIGH NUMBER * E-8 15: 409.59E-04 % UNCERIAINTY IN FLUX BASED RATLEIGH NUMBER IS: 455.89E-05
- 9 99.72E-03 73.00E-01 29.58E-01 13.72E-01 TEMPERATURE BASED RAYLEIGH NUMBER + E-7 IS. 136.42E-03 Z UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS :137.15E-02 FLUX BASED RAYLEIGH NUMBER + E-8 IS: 404.94E-04 Z UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 459.52E-05

REDUCED DATA FOR INPUT POWER 0.7 W BOTTOM BOUNDARY AT 20° C

THE RAW Emf DATA ARE FROM THE FILE: 08021717 THE POWER SETTING PER CHIP WAS: 0.7 WATTS

HIP	QNET(W)	lavg-ls	Nu	ZUNC IN Nu	'
	70.20E-02 TEMPERATURE BASED % UNCERTAINTY IN FLUX BASED RAYLEI % UNCERTAINTY IN	14.24E+00 RAYLEIGH NUMBER THE TEMPERATURE E GH NUMBER * E-8 I FLUX BASED RAYLEI	10.76E+00 + E-7 IS: 293 BASED RAYLEIGH S: 308.85E-03 GH NUMBER IS:	70.34E-02 7.08E-03 NUMBER IS :703.04E-03 3 231.59E-04	3
	70.16E-02 TEMPERATURE BASED % UNCERTAINTY IN FLUX BASED RAYLEI % UNCERTAINTY IN	14.08E+00 RAYLEIGH NUMBER THE TEMPERATURE B GH NUMBER * E-8 I FLUX BASED RAYLEI	10.88E+00 * E-7 IS: 28 ASED RAYLEIGH S: 308.10E-0 GH NUMBER IS:	71.16E-02 3.28E-03 NUMBER IS :711.21E-03 231.71E-04	3
1	70.03E-02 TEMPERATURE BASED % UNCERTAINTY IN FLUX BASED RAYLEI % UNCERTAINTY IN	13.66E+00 RAYLEIGH NUMBER THE TEMPERATURE B GH NUMBER * E-8 I FLUX BASED RAYLEI	11.18E+00 * E-7 IS: 273 RASED RAYLEIGH S: 306.03E-03 GH NUMBER IS:	73.32E-02 3.69E-03 NUMBER IS :732.84E-03 232.17E-04	3
	69.32E-02 TEMPERATURE BASED % UNCERTAINTY IN FLUX BASED RAYLEI % UNCERTAINTY IN 1	I3.10E+00 RAYLEIGH NUMBER THE TEMPERATURE B GH NUMBER * E-8 I FLUX BASED RAYLEI	11.54E+00 * E-7 IS: 260 ASED RAYLEIGH S: 301.00E-03 GH NUMBER IS:	76.47E-02 0.90E-03 NUMBER IS :764.36E-03 234.54E-04	}
	69.61E-02 TEMPERATURE BASED % UNCERTAINTY IN FLUX BASED RAYLEIG % UNCERTAINTY IN 1	13.71E+00 RAYLEIGH NUMBER THE TEMPERATURE B GH NUMBER * E-8 I FLUX BASED RAYLEI	11.08E+00 * E-7 IS: 274 ASED RAYLEIGH S: 304.37E-03 GH NUMBER IS:	73.06E-02 9.81E-03 NUMBER IS :730.23E-03 233.57E-04	3
	69.49E-02 TEMPERATURE BASED % UNCERTAINTY IN FLUX BASED RAYLEI % UNCERTAINTY IN F	14.67E+00 RAYLEIGH NUMBER THE TEMPERATURE B GH NUMBER * E-8 I FLUX BASED RAYLEI	10.34E+00 * E-7 IS: 297 ASED RAYLEIGH S: 307.22E-03 GH NUMBER IS:	68.30E-02 7.03E-03 NUMBER IS :682.63E-03 233.95E-04	

7 70.42E-02 14.32E-00 10.73E-00 63.95E-02 TEMPERATURE BASED RAYLEIGH NUMBER & E-7 IS: 298.35E-03 Z UNCERIAINIY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 639.10E-03 FLUX BASED RAYLEIGH NUMBER & E-8 IS: 310.07E-03 Z UNCERIAINIY IN FUX BASED RAYLEIGH NUMBER IS: 230.88E-04

8 70.63E-02 14.06E+00 10.96E+00 71.2EE-02 TEMPERATURE BASED RAYLEIGH NUMBER + E-7 IS: 282.84E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS :712.17E-03 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 310.07E-03 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 230.19E-04

9 70.07E-02 13.67E+00 11.18E+00 73.27E-02 TEMPERATURE BASED RAYLEIGH NUMBER * E-7 IS: 273.90E-03 2 UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 732.34E-03 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 306.28E-03 2 UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 232.01E-04

REDUCED DATA FOR INPUT POWER 1.5 W BOTTOM BOUNDARY AT 20° C

THE RAW Emf DATA ARE FROM THE FILE: 08030205 THE POWER SETTING PER CHIP WAS: 1.5 WATTS

Nu

%UNC IN Nu

1 15.00E-01 22.08E+00 14.90E+00 45.39E-02 TEHPERATURE BASED RAYLEIGH NUMBER * E-7 IS: 434.85E-03 2 UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 453.37E-03 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 722.22E-03 2 UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 225.19E-04

Tavg-Ts

QNET(N)

- 3 14,95E-01 20.92E-00 15.68E+00 47.92E-02 TEMPERATURE BASED RAYLEIGH NUHBER ± E-7 IS: 453.60E-03 2.UHCERIAINIY IN THE TEMPERATURE BASED RAYLEIGH NUHBER IS: 473.68E-03 FLUX BASED RAYLEIGH NUHBER * E-8 IS: 711.25E-03 2.UHCERIAINIY IN FLUX BASED RAYLEIGH NUHBER IS: 225.71E-04
- 4 14.815-01 21.04E+00 15.43E+00 47.63E-02 TEMPERATURE BASED RAYLEIGH NUMBER + E-7 IS: 457.00E-03 % UNCERTAINT N THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 475.76E-03 FLUX BASED RAYLEIGH NUMBER + E-R IS: 705.05E-03 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 228.02E-04
- 5 14.87E-01 21.15E+00 15.42E+00 47.39E-02 TEMPERATURE BASED RATLEIGH NUMBER * E-7 15: 495.81E-03 2 UNCERTAINTY IN THE TEMPERATURE BASED RATLEIGH NUMBER IS: 473.39E-03 FLUX BASED RATLEIGH NUMBER * E-8 15: 708.81E-03 2 UNCERTAINTY IN FLUX BASED RATLEIGH NUMBER IS: 227.07E-04
- 6 14.84E-01 17.77E+00 18.26E-00 56.38E-02 TEMPERATURE BASED RAYLEIGH NUHBER * E-7 IS: 372.79E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 553.37E-03 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 580.72E-03 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 227.55E-04
- 7 15.04E-01 22.33E+00 14.78E+00 44.90E-02 TEMPERATURE BASED RATLEIGH NUMBER * E-7 IS: 491.49E-03 Z UNCERTAINTY IN THE TEMPERATURE BASED RATLEIGH NUMBER IS: 448.39E-03 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 726.23E-03 Z UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 224.56E-04
- 8 15.09E-01 21.76E+00 15.20E+00 46.06E-02 TEMPERATURE BASED RAYLEIGH NUMBER + E-7 IS: 47.17E-03 2 UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 460.08E-03 FLUX BASED RAYLEIGH NUMBER - E-8 IS: 723.92E-03 2 UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 223.86E-04
- 3 14.97E-01 21.07E-00 15.58E+00 47.58E-02 TEMPERATURE BASED RATLEIGH NUMBER + E-7 IS: 47.58E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RATLEIGH NUMBER IS :475.23E-03 FLUX BASED RATLEIGH NUMBER + E-8 IS: 712.92E-03 % UNCERTAINTY IN FLUX BASED RATLEIGH NUMBER IS: 225.59E-04

REDUCED DATA FOR INPUT POWER 3.0 W BOTTOM BOUNDARY AT 20° C

THE RAW Emf DATA ARE FROM THE FILE: 03041705 THE PUWER SETTING PER CHIP WAS: 3.0 WATTS

.H.2	QNET(W)	Tavg-Ts	Nu	ZUNC IM Nu
1	29.42E-01	36.28E+00	17.97E+00	27.67E-02
	IEMPERATURE BASE	D RAYLEIGH NUMBER	* E-7 IS: 930	6.63E-03
	% UNCERTAINTY IN	THE TEMPERATURE	BASED RAYLEIGH	NUMBER IS :276.00E-03
	FLUX BASED RAYLE	IGH NUMBER * E-B	IS: 168.28E-03	2
	% UNCERTAINTY IN	FLUX BASED RAYLE	IGH NUMBER IS:	194.60E-04
2	29.41E-01 TEMPERATURE BASE % UNCERTAINTY IN FLUX BASED RAYLE % UNCERTAINTY IN	35.68E+00 D RAYLEIGH NUMBER THE TEMPERATURE I IGH NUMBER * E-8 FLUX BASED RAYLE	18.25E+00 * E-7 IS: 91! BASED RAYLEIGH IS: 167.20E-0 IGH NUMBER IS:	28.13E-02 5.94E-03 NUMBER IS :280.60E-03 194.65E-04
3	29.36E-01	33.82E+00	19.20E+00	29.67E-02
	TEMPERATURE BASE	D RAYLEIGH NUMBER	* E-7 IS: 853	2.2BE-03
	% UNCERTAINTY IN	THE TEMPERATURE	BASED RAYLEIGH	NUMBER IS :296.05E-03
	FLU% BASED RAYLE	IGH NUMBER * E-8	IS: 163.66E-03	2
	% UNCERTAINTY IN	FLUX BASED RAYLE	IGH NUMBER IS:	195.00E-04
4	29.06E-01 TEMPERATURE BASE % UNCERTAINTY IN FLUX BASED RAYLE % UNCERTAINTY IN	35.66E+00 D RAYLEIGH NUMBER THE TEMPERATURE I IGH NUMBER * E-8 FLUX BASED RAYLE	18.05E+00 * E-7 IS: 91 BASED RAYLEIGH IS: 165.19E-0 IGH NUMBER IS:	2B.14E-02 5.27E-03 NUMBER IS :2B0.75E-03 196.99E-04
5	29.19E-01	35.27E+00	18.32E+00	28.46E-02
	TEMPERATURE BASE	D RAYLEIGH MUMBER	* E-7 IS: 90	1.62E-03
	% UNCERTAINTY IN	THE TEMPERATURE I	BASED RAYLEIGH	NUMBER IS :283.89E-03
	FLUX BASED RAYLE	IGH NUMBER * E-8	IS: 165.19E-02	2
	% UNCERTAINTY IN	FLUX BASED RAYLE	IGH NUMBER IS:	196.17E-04

6 29.08E-01 32.37E+00 19.85E+00 30.99E-02 TEMPERATURE BASEN THE IGH NUMBER * E-7 IS: 804.05E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RATLEIGH NUMBER IS: 309.31E-03 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 159.62E-02 % UNCERTAINTY IN FLUX BASED RATLEIGH NUMBER IS: 196.B9E-04

7 29.50E-01 37.54E-00 17.42E+00 26.74E-02 TEMPERATURE BASED RAYLEIGH NUMBER * E-7 15: 981.44E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER*IS: :266.69E-03 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 170.99E-02 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 134.07E-04

- 8 29.59E-01 36.22E+00 18.09E+00 27.71E-02 TEMPERATURE BASED RAYLEIGH NUMBER ± E-7 IS: 934.89E-03 % UNCERTAINIT IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 276.38E-03 FLUX BASED RAYLEIGH NUMBER ± E-8 IS: 159.15E-02 % UNCERTAINIT IN FLUX BASED RAYLEIGH NUMBER IS: 193.51E-04
- 9 29.37E-01 34.23E+00 18.9BE+00 29.32E-02 TEMPERATURE BASIN ATTICLEGH NUMBER * E-7 IS: 966.10E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RATLEIGH NUMBER IS: 292.51E-03 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 154.42E-02 % UNCERTAINTY IN FLUX BASED RATLEIGH NUMBER IS: 194.95E-04

TEMPERATURE DATA FOR INPUT POWER 0.1 W BOTTOM BOUNDARY INSULATED

THESE RESULTS ARE STORED IN FILE: 08221255

AMBIENT TEMP WAS: 23.0 C VOLTMETER READING WAS: 1.2134 V BATH TEMP WAS: 10 C-INSUL

ALL TEMPERATURES ARE IN DEGREES CELCIUS

	CENTER	TOP	RIGHT	LEFT	BOTTCM	BACK
CHIP NO1: POWER	15.92E+00 (HATTS):	15.85E+00 10.08E-02	15.05E+00	15.82E+00	15.87E+00	16.36E+00
CHIP NO2: POWER	15.32E+00 (WATTS):	15.95E+00 10.07E-02	15.98E+00	15.87E+00	15.95E+00	16.44E+00
CHIP NO3: POWER	15.71E+00 (WATTS):	15.66E+00 10.05E-02	15.78E+00	15.82E+00	15.86E+00	16.14E+00
CHIP NO4: POWER	15.77E-00 WATTS :	15.93E+00 99.49E-03	15.72E+00	15.64E+00	15.71E+00	16.12E+00
CHIP NOS: POWER	15.77E+00 (WATTS):	15.87E+00 99.89E-02	15.84E+00	15.77E+00	15.85E+00	16.20E+00
CHIP NOS: POWER	17.90E+00 (WATTST:	15.73E+ 0 99.74E-03	15.77E+00	15.71E+00	12.78E+00	16.59E+00
C P NO7: POWER	15.75E+00 WATTS :	15.79E+00 10.11E-02	15.75E+00	15.71E+00	15.84E+00	16.4)E+00
CHIP NO8: POWER	15.85E+00 (WATTS1:	15.36E-00 10.14E-02	15.91E+00	15.825+00	15.83E+00	16.56E+00
CHIP HO9: POWEP	15.56E+00 (WATTS):	15.49E+00 10.05E-02	15.625+00	15.59E+00	15.64E+00	16.15E+00
нЕнт	EICHANGERS BOTTOM: TOP:	TEMPERATURES	5: RIGH 15.976 10.208	LEFT +00 15.97 +00 96.30	=+00 =-01 f	
BACK	PLANE TEMPE	RATURES ARE	:			
	T (55): 15. T (56): 16. T (72): 16. T (73): 16. T (74): 17. T (75): 16. T (76): 16. T (77): 16.	0 E+00 41E+00 0 E+00 73E+00 78E+00 24E+00 42E+00 75E+00 69E+00				

TEMPERATURE DATA FOR INPUT POWER 0.7 W BOTTOM BOUNDARY INSULATED

THESE RESULTS ARE STORED IN FILE: 08222257

AMBIENT TEMP WAS: 21.7 C VOLTMETER READING WAS: 3.22 V BATH TEMP WAS: 10 C-INS

ALL TEMPERATURES ARE IN DEGREES CELCIUS

		CENTER	TOP	RIGHT	LEFT	BOTTOM	BACK
CHIP	NO1: POWER	23.57E+00 (WATTS):	22.96E+00 70.88E-02	22.84E+00	22.84E+00	22.85E+00	25.39E+00
CHIP	NO2: POWER	23.52E+00 (WATTS):	22.57E+00 70.83E-02	22.76E+00	22.30E+00	22.68E+00	25.39E+00
CHIP	NO3: POWER	22.90E+00 (WATTS):	22.62E+00 70.69E-02	22.51E+00	22.47E+00	22.24E+00	24.00E+00
CHIP F	NO4: POWER	23.46E+00 (WATTS):	22,91E+00 69,99E-02	22.73E+00	22.17E+00	22.67E+00	24.75E+00
CHIP	NO5: POWER	23.20E+00 (WAITS):	22.20E+00 70.28E-02	22.27E+00	22.14E+00	22.60E+00	24.21E+00
CHIP	NO6: POWER	26.26E+00 (WATTS):	22.78E+00 70.15E-02	22.23E+00	22,30E+00	18.88E+00	26.38E+00
C P F	NO7: POWER	23.35E+00 (WATTS):	23.15E+00 71.09E-02	22.80E+00	22.60E+00	22.93E+00	25.70E+00
CHIP	NO8: OWER	23.17E+00 (WATTS):	22.97E+00 71.30E-02	22.85E+00	22.70E+00	22.60E+00	26.66E+00
CHIP	NO9: OWER	22.70E+00 (WATTS);	22.48E+00 70.72E-02	22.43E+00	22.26E+00	22.24E+00	25.53E+00
н	IEAT E E 1	EXCHANGERS BOTTOM: TOP:	TEHPERATURES	: RIGHT 17.35E 10.28E	LEFT +00 17.36E +00 97.63E	+00 -01 T	
B	ACK F	PLANE TEMPE	RATURES ARE	:			

T(55):	19.34E+00
T(56):	19.81E+00
T(57):	19.74E+00
T(72):	20.01E+00
T(73):	71.30E-01
T(74):	19.99E+00
T(75):	19.59E+00
1(76):	19.76E+00
T(77):	19,88F+00

TEMPERATURE DATA FOR INPUT POWER 1.1 W BOTTOM BOUNDARY INSULATED

THESE RESULTS ARE STORED IN FILE: 08231010

AMBIENT TEMP WAS: 21.33 C VOLTMETER READING WAS: 4.00 V BATH TEMP WAS: 10 C-INS

ALL TEMPERATURES ARE IN DEGREES CELCIUS

	CENTER	TOP	RIGHT	LEFT	BOTTOM	BACK
CHIP NO1: POWER	28.35E+00 (WATTS):	26.73E+00 10.96E-01	27.12E+00	27.11E+00	27.13E+00	30.82E+00
CHIP NO2: POWER	28.16E+00 (WATTS):	26.70E+00 10.95E-01	26.93E+00	26.29E+00	26.90E+00	30.97E+00
CHIP NO3: POWER	26.96E+00 (WATTS):	26.97E+00 10.93E-01	26.70E+00	26.57E+00	26.26E+00	28.94E+00
CHIP NO4: POWER	28.21E+00 (WAITS):	27.02E+00 10.82E-01	27.14E+00	26.29E+00	27.07E+00	30.17E+00
CHIP NO5: POWER	27.75E+00 (WATTS):	26.13E+00 10.87E-01	26.25E+00	26.09E+00	26.86E+00	29.20E+00
CHIP NO6: POWER	27.17E+00 (WATTS):	27.20E+00 10.84E-01	26.33E+00	26.45E+00	25.80E+00	32.61E+00
C' TP NO7: POWER	28.65E+00 (WATTS):	27.60E+00 10.99E-01	27.07E+00	26.77E+00	27.15E+00	31.29E+00
CHIP NO8: POWER	27.65E+00 (WAITS):	26.99E+00 11.02E-01	27.08E+00	26.92E+00	26.57E+00	32.87E+00
CHIP NO9: POWER	26.81E+00 (WATTS):	26.65E+00 10.93E-01	26.59E+00	26.36E+00	26.23E+00	31.29E+00

RIGHT	LEFT	
18.43E+00	18.43E+00	
10.21E+00	97.25E-01	1
	RIGHT 18.43E+00 10.21E+00	: RIGHT LEFT 18.43E+00 18.43E+00 10.21E+00 97.25E-01

BACK PLANE TEMPERATURES ARE :

T(55):	21.49E+00
T(56):	22.00E+00
T(57):	22.27E+00
T(72):	22.32E+00
T(73):	21.94E+00
T(74):	22.22E+00
T(75):	22.04E+00
T(76):	21.97E+00
T(77):	22.12E+00

TEMPERATURE DATA FOR INPUT POWER 3.0 W BOTTOM BOUNDARY INSULATED

THESE RESULTS ARE STORED IN FILE: 08231310

AMBIENT TEMP WAS: 23 C VOLTMETER READING WAS: 4.00 V BATH TEMP WAS: 10 C-INS

ALL TEMPERATURES ARE IN DEGREES CELCIUS

	CENTER	TOP	RIGHT	LEFT	BOTTOM	BACK
CHIP_N01: POWER	54.28E+00 (WATTS):	49.66E+00 30.12E-01	50.72E+00	50.63E+00	50.34E+00	59.54E+00
CHIP NO2: POWER	53.84E+00 (WAITS):	49.73E+00 30.11E-01	50.52E+00	48.65E+00	50.06E+00	60.06E+00
CHIP_NO3: POWER	50.25E+00 (WATTS):	50.25E+00 30.06E-01	49.56E+00	49.03E+00	47.98E+00	55.22E+00
CHIP NO4: POWER	53.66E+00 (WATTS):	49.30E+00 [.] 29.77E-01	50.54E+00	48.37E+00	50.35E+00	58.19E+00
CHIP NO5: POWER	52.76E+00 (WAITS):	47.84E+00 29.89E-01	48.71E+00	48.29E+00	49.81E+00	55.75E+00
CHIP NO6: POWER	55.76E+00 (WATTS):	51.99E+00 29.78E-01	48.65E+00	49.14E+00	50.78E+00	70.28E+00
C TP NO7: POWER	55.44E+00 (WATTS):	51.67E+00 30.21E-01	50.76E+00	50.15E+00	50.57E+00	60.78E+00
CHIP NO8: POWER	52.46E+00 (WATIS):	51.07E+00 30.30E-01	51.00E+00	50.88E+00	50.31E+00	67.37E+00
CHIP NO9: POWER	50.77E+00 (WATTS):	50.34E+00 30.06E-01	49.91E+00	49.40E+00	49.60E+00	51.43E+00
HEAT E E T	XCHANGERS BOTTOM: OP:	TEMPERATURES	: RIGHT 21.94E 11.02E	LEFT +00 21.96E +00 98.81E	+00 -01	

*

BACK PLANE TEMPERATURES ARE :

 T(55):
 32.74E+00

 T(56):
 34.2EE+00

 T(57):
 36.45E+00

 T(72):
 35.4HE+00

 T(73):
 34.76E+00

 T(74):
 35.18E+00

 T(75):
 35.95E+00

 T(75):
 34.28E+00

 T(75):
 34.30E+00

REDUCED DATA FOR INPUT POWER 0.1 W BOTTOM BOUNDARY INSULATED

THE RAW Emi DATA ARE FROM THE FILE: 08221255 THE POWER SETTING PER CHIP WAS: 0.1 WATTS

- CHIP
 ONET(H)
 Tavg-Ts
 Nu
 ZUNC IN Nu

 1
 10.06E-02
 59.19E-01
 35.91E-01
 16.93E-01

 TEMPERATURE BASED RAYLEIGH NUMBER 4: E-4
 15:108.65E-03
 2
 2
 2

 VUNCETIAINT IN THE TEMPERATURE DASED RAYLEIGH NUMBER 15:169.28E-02
 FLUX BASED RAYLEIGH NUMBER 4: E-4
 15:401.14E-04
 394.13E-05

 VUNCETAINT IN FLUX BASED RAYLEIGH NUMBER 15: 394.13E-05
 5
 394.13E-05
 5
 5
- 2 10.05E-02 60.09E-01 36.31E-01 16.67E-01 TEMPERATURE BASED RALLEIGH NUMBER * E-7 IS: 110.46E-03 2 UNCERTAINT IN THE TEMPERATURE BASED RAILEIGH NUMBER IS: 166.74E-02 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 401.11E-04 2 UNCERTAINT IN FLUX BASED RAYLEIGH NUMBER IS: 394.58E-05
- 3 10.03E-02 53.46E-01 37.24E-01 17.14E-01 TEMPERATURE BASED PAYLEIGH NUMBER * E-7 IS: 107.28E-03 2 UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 171.38E-02 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 399.54E-04 2 UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 395.38E-05
- 4 99.33E-03 53.11E-01 37.11E-01 17.24E-01 TEMPERATURE BASED RAYLLIGH NUMBER * E-7 IS: 106.58E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 172.43E-02 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 395.51E-04 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 399.24E-05
- 5 99.73E-03 58.84E-01 36.79E-01 17.03E-01 TEMPERATURE BASED RAYLEIGH NUMBER + E-7 IS: 108.02E-03 % UNCERTAINT N THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 170.27E-02 FLUX BASED RAYLEIGH NUMBER + E-8 IS: 397.44E-04 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 397.65E-05
- 6 99.58E-03 63.05E-01 34.29E-01 15.89E-01 TEMPERATURE BASED RAYLEIGH NUMBER * E-7 IS: 116.29E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 158.90E-02 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 398.81E-04 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 398.24E-05
- 7 10.09E-02 58.34E-01 37.56E-01 17.17E-01 TEHFERATURE BASER ARTLEIGH NUMBER * E-7 IS: 107.04E-03 2 UNCERTAINTY IN THE TEMFERATURE BASED RAYLEIGH NUMBER IS: 171.73E-02 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 402.00E-04 2 UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 332.90E-05
- 8 10.12E-02 59.41E-01 36.98E-01 16.87E-01 TEMPERATURE BASED RAYLEIGH NUMBER + E-7 IS: 109.12E-03 % UNCERTAINITY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS :168.66E-02 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 403.56E-04 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 391.87E-05
- 9 10.04E-02 56.68E-01 38.43E-01 17.68E-01 TEMPERATURE BASED RAYLEIGH NUMBER * E-7 IS: 103.80E-03 % UNCERTAINTY IN THE TEMPERATURE DASED RAYLEIGH NUMBER IS: 176.77E-02 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 399.35E-04 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 395.13E-05

REDUCED DATA FOR INPUT POWER 0.7 W BOTTOM BOUNDARY INSULATED

THE RAN Emf DATA ARE FROM THE FILE: 08222257 THE PONER SETTING PER CHIP WAS: 0.7 WATTS

CHIP	QNET(W)	Tavg-Ts	Nu	ZUNC IN Nu /	
1	70.13E-02 TEMPERATURE BAS % UNCERTAINTY I FLUX BASED RAYL % UNCERTAINTY I	13.10E+00 ED RAYLEIGH NUMBER N THE TEMPERATURE B EIGH NUMBER * E-8 I N FLUX BASED RAYLEI	11.67E+00 * E-7 IS: 261 ASED RAYLEIGH S: 304.66E-03 GH NUMBER IS:	76.47E-02 .03E-03 NUMBER IS :764.35E-03 234.56E-04	
2	70.07E-02 TEMPERATURE BAS % UNCERTAINTY II FLUX BASED RAYL % UNCERTAINTY II	12,85E+00 ED RAYLEIGH NUMBER N THE TEMPERATURE B EIGH NUMBER ★ E-8 I N FLUX BASED RAYLEI	11.89E+00 * E-7 IS: 255 ASED RAYLEIGH S: 303.54E-03 GH NUMBER IS:	77.95E-02 .36E-03 NUMBER IS :779.20E-03 234.75E-04	
3	69.94E-02 TEMPERATURE BASI % UNCERTAINTY I. FLUX BASED RAYLI % UNCERTAINTY I	12.59E+00 ED RAYLEIGH NUMBER N THE TEMPERATURE B EIGH NUMBER ← E-8 I N FLUX BASED RAYLEI	12.11E+00 * E-7 IS: 249 ASED RAYLEIGH S: 302.04E-03 GH NUMBER IS:	79.57E-02 .47E-03 NUMBER IS :795.34E-03 235.21E-04	
1	63.24E-02 TEMPERATURE BAS % UNCERTAINTY IN FLUX BASED RAYL % UNCERTAINTY IN	12.82E+00 ED RAYLEIGH NUMBER 1 THE TEMPERATURE BI EIGH NUMBER * E-8 I N FLUX BASED RAYLEI	11.78E+00 * E-7 IS: 254 ASED RAYLEIGH S: 299.83E-03 GH NUMBER IS:	78.16E-02 .59E-03 NUMBER IS :781.28E-03 237.56E-04	
5	69.53E-02 TEMPERATURE BASE % UNCERTAINTY IN FLUX BASED RAYLE % UNCERTAINTY IN	12,54E+00 ED RAYLEIGH NUMBER N THE TEMPERATURE B EIGH NUMBER * E-8 I N FLUX BASED RAYLEI N FLUX BASED RAYLEI	12.08E+00 * E-7 IS: 248 ASED RAYLEIGH S: 300.13E-03 GH NUMBER IS:	79.88E-02 .36E-03 NUMBER IS :798.47E-03 236.58E-04	
5	69.40E-02 TEMPERATURE BASI % UNCERTAINTY IN FLUX BASED RAYLI % UNCERTAINTY IN	13.34E+00 ED RAYLEIGH NUMBER N THE TEMPERATURE BA EIGH NUMBER * E-8 I N FLUX BASED RAYLEIG	11.35E+00 ★ E-7 IS: 266 ASED RAYLEIGH S: 302.30E-03 GH NUMBER IS:	75.14E-02 .31E-03 NUMBER IS :751.07E-03 237.02E-04	

- 7 70.34E-02 13.12E+00 11.70E+00 76.40E-02 TEMPERATURE BASED RATLEIGH NUMBER * E-7 IS: 261.31E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RATLEIGH NUMBER IS: 763.62E-03 FLUX BASED RATLEIGH NUMBER * E-8 IS: 305.62E-03 % UNCERTAINTY IN FLUX BASED RATLEIGH NUMBER IS: 233.86E-04
- 8 70,55E-02 12.88E+00 11.95E+00 77.82E-02 TEMPERATURE BASED RAYLEIGH NUMBER + E-7 IS: 255.86E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS :777.86E-03 FLUX BASED RAYLEIGH NUMBER + E-8 IS: 305.69E-03 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 233.16E-04
- 9 69.97E-02 12.44E+00 12.26E+00 80.54E-02 TEMPERATURE BASED RAYLEIGH NUMBER * E-7 IS: 246.04E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 805.10E-03 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 301.64E-03 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 235.11E-04

REDUCED DATA FOR INPUT POWER 1.1 W BOTTOM BOUNDARY INSULATED

THE RAW Emf DATA ARE FROM THE FILE: 08231010 THE POWER SETTING PER CHIP WAS: 1.1 WATTS

 CHIP
 ONET(4)
 Tavg-Ts
 Hu
 ZUNC IN Nu

 1
 10.88E-01
 1.52E+00
 13.52E+00
 57.17E-02

 TEMPERATURE BASED RATLEIGH NUMBER & E-7 IS:
 365.80E-03
 2
 UNCERTAINTY IN THE TEMPERATURE BASED RATLEIGH NUMBER IS: 571.25E-03

 FLUX BASED RATLEIGH NUMBER & E-9 IS:
 494.53E-03
 2
 UNCERTAINTY IN FLUX BASED RATLEIGH NUMBER IS: 226.98E-04

- 2 10.83E-01 17.19E+00 13.77E+00 58.29E-02 TEMPERATURE BASED RAYLEIGH NUMBER * E-7 IS: 357.49E-03 % UNCERIAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS :582.43E-03 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 422.30E-03 % UNCERIAINTY IN FUX BASED RAYLEIGH NUMBER IS: 227.14E-04
- 3 10.91E-01 16.77E+00 14.09E+00 59.75E-02 TEMPERATURE BASED RAYLEIGH NUMBER * E-7 IS: 347.17E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 557.04E-03 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 489.01E-03 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 227.58E-04
- 4 10,70E-01 17.30E+00 13.52E+00 57.93E-02 TEMPERATURE BASED RAYLEIGH NUMBER ± E-7 IS: 360.14E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 578.80E-03 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 407.09E-03 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 229.85E-04
- 5 10.75E-01 15.78E+00 14.00E+00 59.71E-02 TEMPERATURE BASED RAYLEIGH NUMBER + E-7 IS: 347.42E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS :596.67E-03 FLUX BASED RAYLEIGH NUMBER + E-8 IS: 495.30E-03 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 228.88E-04
- 6 10.73E-01 15.70E400 14.03E400 50.00E-02 TEMPERATURE BASED RAYLEIGH NUMBER * E-7 IS: 345.45E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS :599.56E-03 FLU% BASED RAYLEIGH NUMBER * E-8 IS: 494.82E-03 % UNCERTAINTY IN FLU% BASED RAYLEIGH NUMBER IS: 229.37E-04
- 7 10.97E-01 77.61E-00 13.50E-00 55.91E-02 TEMPERATURE BASE MAYLEIGH NUMBER * E-7 IS: 367.76E 303 Z UNCERIAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS :568.68E-03 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 496.47E-03 Z UNCERIAINT IN FLUX BASED RAYLEIGH NUMBER IS: 226.30E-04
- 8 10.90E-01 17.22E+00 13.85E+00 58.21E-02 TEMPERATURE BASED RAYLEIGH NUMBER ± E-7 IS: 358.03E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 581.69E-03 FLUX BASED RAYLEIGH NUMBER ± E-8 IS: 495.81E-03 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 225.59E-04
- 9 10.81E-01 16.61E-00 14.23E*00 60.32E-02 TEMPERATURE BASED RAYLEIGH NUMBER * E-7 IS: 333.28E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 602.77E-03 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 408.34E-03 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 227.49E-04

REDUCED DATA FOR INPUT POWER 3.0 W BOTTOM BOUNDARY INSULATED

THE RAW Emf DATA ARE FROM THE FILE: 08231310 THE POWER SETTING PER CHIP WAS: 3.0 WATTS

CHIP	ONET(W)	Tavg-Ts	Nu	ZUNC IN Nu
1	29.78E-01 TEMPERATURE BASED % UNCERTAINTY IN FLUX BASED RAYLE % UNCERTAINTY IN	41.31E+00 CRAYLEIGH NUMBER THE TEMPERATURE E GH NUMBER * E-8 D FLUX BASED RAYLE	16.01E+00 * E-7 IS: 110 BASED RAYLEIGH IS: 177.54E-02 IGH NUMBER IS:	24.31E-02 .90E-02 NUMBER IS :242.30E-03 202.57E-04
2	29.77E-01 TEMPERATURE BASEL % UNCERTAINTY IN FLUX BASED RAYLE % UNCERTAINTY IN	40.60E+00 D RAYLEIGH NUMBER THE TEMPERATURE E IGH NUMBER * E-8 D FLUX BASED RAYLED	16.28E+00 * E-7 IS: 108 BASED RAYLEIGH IS: 176.18E-02 GH NUMBER IS:	24.74E-02 .25E-02 NUMBER IS :246.54E-03 202.65E-04
3	29.72E-01 TEMPERATURE BASED % UNCERTAINTY IN FLUX BASED RAYLED % UNCERTAINTY IN	39.13E+00 D RAYLEIGH NUMBER THE TEMPERATURE E IGH NUMBER * E-8 D FLUX BASED RAYLED	16.84E+00 * E-7 IS: 102 BASED RAYLEIGH IS: 173.21E-02 IGH NUMBER IS:	25.66E-02 .84E-02 NUMBER IS :255.82E-03 203.01E-04
4	29.42E-01 TEMPERATURE BASEI % UNCERTAINTY IN FLUX BASED RAYLEJ % UNCERTAINTY IN	40.51E+00 D RAYLEIGH NUMBER THE TEMPERATURE E IGH NUMBER * E-8 D FLUX BASED RAYLED	16.12E+00 * E-7 IS: 107 RASED RAYLEIGH IS: 173.98E-02 GH NUMBER IS:	24.79E-02 .92E-02 NUMBER IS :247.08E-03 205.02E-04
5	29.55E-01 TEMPERATURE BASED % UNCERTAINTY IN FLUX BASED RAYLEJ % UNCERTAINTY IN	39.52E+00 NAYLEIGH NUMBER THE TEMPERATURE E GH NUMBER * E-8 I FLUX BASED RAYLEI	16.59E+00 * E-7 IS: 104 ASED RAYLEIGH S: 172.94E-02 GH NUMBER IS:	25.41E-02 .27E-02 NUMBER IS :253.28E-03 204.15E-04
6	29.44E-01 TEMPERATURE BASED % UNCERTAINTY IN FLUX BASED RAYLEJ % UNCERTAINTY IN	41.15E+00) RAYLEIGH NUMBER THE TEMPERATURE E GH NUMBER * E-8] FLUX BASED RAYLEI	15.89E+00 * E-7 IS: 110 ASED RAYLEIGH S: 175.19E-02 GH NUMBER IS:	24.42E-02 .27E-02 NUMBER IS :243.29E-03 204.93E-04
7	29.87E-01 TEMPERATURE BASED % UNCERTAINTY IN FLUX BASED RAYLEI % UNCERTAINTY IN	41.77E+00 RAYLEIGH NUMBER THE TEMPERATURE E GH NUMBER * E-8 I FLUX BASED RAYLEI	15.89E+00 * E-7 IS: 112 HASED RAYLEIGH S: 178.94E-02 GH NUMBER IS:	24.05E-02 .63E-02 NUMBER IS :239.64E-03 201.94E-04
8	29.96E-01	40.95E+00	16.25E+00	24.53E-02

- TEMPERATURE BASED RAYLEIGH NUMBER * E-7 IS: 109.55E-02 % UNCERIAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 244.43E-03 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 177.96E-02 % UNCERIAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 201.34E-04
- 9 29.72E-01 39.63E+00 16.64E+00 25.34E-02 TEMPERATURE BASED RALLEIGH NUMBER * E-7 IS: 104.65E-02 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 252.60E-03 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 174.11E-02 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 203.00E-04

TEMPERATURE DATA FOR INPUT POWER 0.1 W CHAMBER WIDTH = 30 mm

RESULTS ARE STORED IN FILE: 10161810

	EXPERI	MENT IT TEM	CARRI P (CE	ED OUT	T AT		24	33				
	TEMPER	ENP ATURE	READ	U C-10 INGS 1	J C IN DE	GREE	s cr	I S TH	ç			
	1010 00	CENTE	R	TOP	RIGH	I	LEF	.coro [BC	MOLION	BA	СК
CHIF	NO1:	12.80	6 12	.761	12.7	36	12.7	71	12.	616	15.	431
CUTE	PUWER		5):	.098	33 12 F	0.1	12 0	0.01	12	010	10	400
CITT	POWER	WATT	S):	.099	72.3	51	12.0	001	12.	010	13.	430
CHIP	N03:	13.09	9 12	.956	00.0	00	12.9	986	13.	076	15.	451
	POWER	(WAII	5):	.099	96							
CHIP	POLIE D	12.76	4 12	.731	12.5	36	12.5	574	12.	484	15.	441
CHIP	N05:	12.83	1 12	.894	12.8	36	12.8	324	12.	801	15.	446
	POWER	(WATT	S):	.099	93							
CHIP	N06:	13.01	9 12	.914	12.9	79	11.8	358	12.	746	15.	448
СНТР	PUWER	12 68	57: 9 12	686	12 7	06	12 6	8/	12	559	15	445
CHI	POWER	WATT	s):'`	.099	32	00	12.10	-00	12.	555	1.5.	5
CHIP	N08:	13.03	9 12	.941	12.9	66	00.0	000	12.	901	15.	442
CUTP	PUWER	(WALL 10 25)	5):	.099	12 0	24	12 1	44	12	1.0.0	15	445
CUT	POWER	WATT	s):	. 099	32	34	1.5.1	44	13.	144	15.	
	HEAT E	XCHAN	GERS	TEMPER	RATUR	ES:	,	RIGH	1	CENTER		LEFI
	. U		:				1	0 03	2	10.012	10	- 997
		01.						0.05	·	00.000	10	* U-12
	BACK P	LANE	TEMPER	RATURE	S :							
	I(55):	12.1	556									
	1(50);	12	709									
	T(74):	13.	131									
	T(75):	13.	561									
	1(76):	13.	671							,		
	1(77):	13.	366									
	SOURCE	VOLT	AGE:	1.225	5							
	VOL TAG	E TO	THE HE	ALERS	5 :							
	CHIP #	1:	.97	2								
	CHIP #	2:	1.02	/								
	CHIP #	4.	1.02	<u><</u>								
	CHIP #	5:	. 361	3								
	CHIP #	6:	1.022	2								
	CHIP #	7:	1.02	3								
	CHIP #	8:	1.02	5								
TEMPERATURE DATA FOR INPUT POWER 0.7 W CHAMBER WIDTH = 30 mm

RESULTS ARE STORED IN FILE: 10170950 EXPERIMENT CARRIED OUT AT AMBIENT TEMP (CELSIUS) OF: 24.78 BATH TEMP : 10 C-10 C TEMPERATURE READINGS IN DEGREES CELSIUS CENTER TOP RIGHT LEFT BOITOM BACK CHIP NO1: 21.48 21.22 21.31 24.28 21.08 20.01 POWER (WATTS): .708 CHIP NO2: 22.18 21.50 POWER (WATTS): .712 18.45 21.41 20.88 24.34 CHIP NO3: 22.65 21.48 00.00 POWER (WATTS): .719 21.56 21.98 24.44 CHIP NO4: 21.68 21.26 POWER (WATTS): ,715 20.78 21.12 20.37 24.39 CHIP NO5: 21.93 21.19 POWER (WATTS): .718 24.42 21.53 21.74 21.48 CHIP NO6: 22.75 21.81 22.07 POWER (WATTS): .721 20.73 20.12 24.48 CHIP NO7: 21.14 20.83 2 POWER (WATTS): .719 21.34 20.95 19.34 24.44 CHIP N08: 22.00 21.42 21.32 00.00 20.87 24.43 POWER (WAITS): .718 CHIP N09: 22.65 20.64 18.15 POWER (WAITS): .717 22.02 21.83 24.42 ,717 LEFT HEAT EXCHANGERS TEMPERATURES: RIGHT CENTER 10.017 09.972 BOITOM: 09.922 TOP: 09.977 00.000 10.060 BACK PLANE TEMPERATURES 1(55): 15.191 I(56):15.611 1(57): 14.265 I(74): 15.651 1(75): 16.079 1(76): 16.521 ۲ T(77): 15.350 SOURCE VOLTAGE: 3,288 VOLTAGE TO THE HEATERS : CHIP #1: 2.610 CHIP #2: 2.756 2.743 CHIP #3: CHIP #4: 2.747 CHIP #5: 2.597 CHIP #6: 2.741 CHIP #7: 2.743 CHIP #8: 2.744 CHIP #9: 2.745

TEMPERATURE DATA FOR INPUT POWER 1.1 W CHAMBER WIDTH = 30 mm

RESULTS ARE STORED IN FILE: 10171720

EXPERIMENT CARRIED OUT AT AMBIENT TEMP (CELSIUS) OF:	25.94		
BATH TEMP : 10 C-10 C		10	
TEMPERATURE READINGS IN DEGREE	S CELSI	JS	DOCK
CHIP NO1: 26.38 25.79 25.94	26.17	24.21	29.857
CHIP NO2: 27.34 26.00 22.01 POWER (WAITS): 1.099	26.17	25.62	29.96
CHIP N03: 27.67 25.73 00.00 POWER (WAIIS): 1.1093	26.08	26.69	30.11
CHIP N04: 26.74 26.07 25.51	26.00	24.85	30.02
CHIP N05: 29.78 25.86 26.40	26.71	26.35	30.08
CHIP NO6: 27.51 25.54 26.74	25.65	24.17	30.16
CHIP NOT: 25.80 25.40 26.18	25.63	22.98	30.10
CHIP NO8: 27.06 25.80 26.15	00.00	25.29	30.11
CHIP N09: 27.79 24.71 21.36 POWER (WATTS): 1.110	26.94	26.60	30.11
HEAT EXCHANGERS TEMPERATURES: BOTTOM: TOP:	RIG 09.93 10.0	HT CENTER 24 10.015 10 00.000	LEFT 09.987 10.068
BACK PLANE TEMPERATURES : T(55): 15.88 T(55): 17.48 T(57): 15.70 T(74): 17.57 T(75): 18.00 T(75): 18.09 T(77): 17.08		۲	
SOURCE VOLTAGE: 4.085			
- VOLTAGE TO THE HEATERS : CHIP #1: 3.244 CHIP #2: 3.224 CHIP #3: 3.408 CHIP #3: 3.408 CHIP #4: 3.413 CHIP #5: 3.228 CHIP #6: 3.406 CHIP #7: 3.408 CHIP #8: 3.408 CHIP #9: 3.408			

TEMPERATURE DATA FOR INPUT POWER 1.5 W CHAMBER WIDTH = 30 mm

RESULTS ARE STORED IN FILE: 10181020

EXPERIMENT CARRIED OUT AT AMBIENT TEMP (CELSIUS) OF:	23.94		
BATH TEMP : 10 C-10 C			
TEMPERATURE READINGS IN DEGREE	S CELSI	JS	
CHIP NO1: 33.07 32.50 32.62	12.72	80110H 29.91	BACK 35.55
CHIP NO2: 34.32 32.62 27.17 Phile (UATTS): 1.484	32.75	31.80	35.68
CHIP NO3: 34.63 32.10 00.00 POWER (HAITS): 1.5077	32.62	33.39	35.89
CHIP N04: 33.56 32.40 31.90 POWER (WAITS): 1.501	32.49	30.83	35,79
CHIP NO5: 33.39 32.19 32.67 POWER (WAITS): 1.506	33.16	32.64	35.87
CHIP NO6: 34.02 31.20 33.07 POWER (WATTS): 1.513	32.41	29.59	35.97
CHIP NO7: 32.02 30.79 32.47 POWER (WAITS): 1.508	31.73	27.98	35.89
CHIP NO8: 33.89 32.28 32.71 POWER (WATTS): 1.507	00.00	31.39	35.89
CHIP N09: 34.69 31.22 26.04 POWER (WATTS): 1.507	33.41	33.00	35.88
HEAT EXCHANGERS TEMPERATURES:	RIG	IT CENT	ER LEFT
10P:	10.10		10.126
BACK PLANE TEMPERATURES : T(55): 19.59 T(56): 20.25			
I(5/): 17.80 I(74): 21.09 I(75): 20.76 I(75): 21.47			
1(77): 19.69			
SOURCE VOLTAGE: 4.767		ŕ	
VOLTAGE TO THE HEATERS : CHIP #1: 3.787			
CHIP #2: 3.997 CHIP #3: 3.979			
CHIP #4: 3.983 CHIP #5: 3.767			
CHIP #6: 3.975 CHIP #7: 3.979			
CHIP #8: 3.979 CHIP #9: 3.979			
THESE RESULTS ARE NO	DW STORED	ON DISK	FASTSCAN

FILE: 30MH10R

TEMPERATURE DATA FOR INPUT POWER 2.5 W CHAMBER WIDTH = 30 mm

RESULTS ARE STORED IN FILE: 10182338 EXPERIMENT CARRIED OUT AT AMBIENT TEMP (CELSIUS) OF: 23.17 BATH TEMP : 10 C TEMPERATURE READINGS IN DEGREES CELSIUS CENTER TOP RIGHT LEFT BOITOM BACK CHIP N01: 42.47 41.80 42.04 37.20 49.73 41.39 POWER (WATTS): 2.461 CHIP NO2: 44.31 40.93 41.68 41.68 40.14 49.93 2.475 POWER (WATTS): CHIP NO3: 44.77 41.10 00.00 41.43 42.66 50.28 POWER (WAITS): 2.4985 CHIP N04: 42.78 40.79 41.00 38.73 50.08 40.47 POWER (WATTS): 2.485 CHIP N05: 42.58 42.08 41.60 42.36 41.83 50.20 POWER (WATTS): 2.494 CHIP NO6: 42.77 38.65 POWER (WATTS): 2.507 41.30 41.37 35.79 50.41 CHIP N07: 40.63 39.59 40.51 41.08 34.17 50.25 2.497 POWER (WATTS): CHIP N08: 42.02 39.95 40.79 00.00 37.88 50.27 2.498 POWER (WAITS): CHIP N09: 42.77 37.10 41.32 41.32 40.60 50.24 POWER (WATTS): 2,496 HEAT EXCHANGERS TEMPERATURES: RIGHT CENTER LEFT BUITOM: 10.020 10.110 10.065 TOP: 09.748 00.000 10.015 BACK PLANE TEMPERATURES : T(55): 21.28 T(56): 22.30 1(57): 19.47 23.34 I(74):1(75): 22.77 1(76): 23.81 ۲ 21.70 SOURCE VOLTAGE: 6.142 VOLTAGE TO THE HEATERS : CHIP #1: 4,881 CHIP #2: 5.152 CHIP #3: 5.128 CHIP #4: 5.135 4.859 CHIP #5: CHIP #6: 5.124 5.129 CHIP #7: CHIP #8: 5.129 CHIP #9: 5.129

TEMPERATURE DATA FOR INPUT POWER 3.0 W CHAMBER WIDTH = 30 mm

RESULTS ARE STORED IN FILE: 10232224 EXPERIMENT CARRIED OUT AT 22.83 AMBIENT TEMP (CELSIUS) OF: BATH TEMP : 10 C TEMPERATURE READINGS IN DEGREES CELSIUS CENTER TOP RIGHT **IFFT** BOTIOM BACK CHIP NO1: 50.66 49.62 49.97 49.07 43.61 57.87 POWER (WATTS): 3.022 CHIP NO2: 52.71 47. POWER (WATTS): 47.72 49.42 49.42 46.37 58.10 3.038 CHIP N03: 52.51 48.65 00.00 47.22 49.87 58.53 POWER (WAITS): 3.0672 CHIP N04: 51.15 47.96 POWER (WATTS): 3.051 48.59 48.79 46.00 58.30 CHIP N05: 50.48 48.36 50.54 48.61 58.47 49.36 POWER (WATTS): 3.053 CHIP NO6: 51.67 42.15 POWER (WATTS): 3.079 48.38 47.63 46.09 58.70 CHIP N07: 48.27 46.25 48.70 48.07 39.78 58.52 POWER (WATTS): 3.066 45.58 CHIP N08: 49.10 48.05 00.00 44.02 58.53 POWER (WATTS): 3.067 CHIP N09: 50.71 41.39 43.01 43.01 45.34 58.49 POWER (WATIS): 3.064 HEAT EXCHANGERS TEMPERATURES: RIGHT CENTER LEFT BOITON: 10.057 10.166 10.176 TOP: 10.073 00.000 10.163 BACK PLANE TEMPERATURES : 1(55): 24.75 1(56): 26.51 I(57): 22.64 I(74):28.00 1(75): 26.95 1(76): 28.63 \$ T(77): 25.41 SOURCE VOLTAGE: 6.807 VOLTAGE TO THE HEATERS : CHIP #1: 5.411 CHIP #2: 5.712 CHIP #3: 5.685 CHIP #4: 5.692 CHIP #5: 5.385 CHIP #6: 5.680 CHIP #7: 5.685 CHIP #8: 5.685 CHIP #9: 5.686

REDUCED DATA FOR INPUT POWER 0.1 W CHAMBER WIDTH = 30 mm

THE RAW Emf DATA ARE FROM THE FILE: 10161810 THE POWER SETTING PER CHIP WAS: 0.1 $\rm M$ THE DISTANCE TO THE FRONT WALL WAS 30 MM

CHIP ONET(W) Tavg-Is Nul Nu2

- 1 .10 2.76 23.19 10.85 FLUX BASED RAYLEIGH NUMBER * E-9 IS: .31 AVERAGE TEMPERATURE: 12.861 SINK TEMPERATURE: 10.104
- 2 .10 2.82 22.77 10.66 FLUX BASED RAYLEJCH NUMBER * E-9 IS: .31 AVERAGE TEMPERATURE: 12.925 SINK TEMPERATURE: 10.104
- 3 .10 3.04 21.32 9.98 FLUX BASED RAYLEIGH NUMBER * E-9 IS: .31 AVERAGE IEMPERATURE: 13.144 SINK TEMPERATURE: 10.104
- 4 .10 2.63 24.48 11.46 FLUX BASED RAYLEIGH NUMBER * E-9 IS: .31 AVERAGE TEMPERATURE: 12.734 SINK TEMPERATURE: 10.104
- 5 .10 2.83 22.82 10.68 FLUX BASED RAYLEICH NUMBER * E-9 IS: .31 AVERAGE IEMPERATURE: 12.934 SINK IEMPERATURE: 10.104
- 6 .10 2.68 24.11 11.28 FLUX BASED RAYLEJCH NUMBER * E-9 IS: .31 AVERAGE IEMPERATURE: 12.788 SINK IEMPERATURE: 10.104
- 7 .10 2.68 24.10 11.28 FLUX BASED RAYLEJCH NUMBER * E-9 IS: .31 AVERAGE TEMPERATURE: 12.782 SINK TEMPERATURE: 10.104
- 8 .10 2.39 21.58 10.10 FLUX BASED RAYLEIGH NUMBER * E-9 IS: .31 AVERAGE TEMPERATURE: 13.089 SINK TEMPERATURE: 10.104
- 9 .10 3.10 20.84 9.75 FLUX BASED RAYLEJGH NUMBER * E-9 IS: .31 AVERAGE IEMPERATURE: 13.202 SINK TEMPERATURE: 10.104

REDUCED DATA FOR INPUT POWER 0.7 W CHAMBER WIDTH = 30 mm

THE RAW Emf DATA ARE FROM THE FILE: 10170950 THE POWER SETTING FER CHIP HAS: 0.7 W THE DISTANCE TO THE FRONT WALL HAS 30 MM

CHIP QNET(W) Tavg-Is Nul Nu2

- 1 .70 11.22 40.87 19.12 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 2.41 AVERAGE TEMPERATURE: 21.294 SINK TEMPERATURE: 10.073
- 2 .71 10.92 42.23 19.76 FLUX BASED RAYLEJGH NUMRER * E-9 IS: 2.42 AVERAGE TEMPERATURE: 20.990 SINK TEMPERATURE: 10.073
- 3 .71 12.11 38.48 18.00 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 2.48 AVERAGE TEMPERATURE: 22.185 SINK TEMPERATURE: 10.073
- 4 .71 11.20 41.37 19.36 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 2.44 AVERAGE TEMPERATURE: 21.273 SINK TEMPERATURE: 10.073
- 5 .71 11.71 39.73 18.59 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 2.46 AVERAGE TEMPERATURE: 21.783 SINK TEMPERATURE: 10.073
- 6 .72 11.81 39.61 18.53 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 2.48 AVERAGE TEMPERATURE: 21.878 SINK TEMPERATURE: 10.073
- 7 .71 10.99 42.38 19.83 FLUX BASED RAYLEJGH NUMBER * E-9 IS: 2.45 AVERAGE ILMPERATURE: 21.066 SINK IEMPERATURE: 10.073
- 8 .71 11.61 40.07 18.75 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 2.46 AVERAGE TEMPERATURE: 21.685 SINK TEMPERATURE: 10.073
- 9 .71 11.16 41.64 19.48 FLUX BASED RAYLEIGH NUMBER * F-9 IS: 2.44 AVERAGE TEMPERATURE: 21.235 SINK TEMPERATURE: 10.073

REDUCED DATA FOR INPUT POWER 1.1 W CHAMBER WIDTH = 30 mm

THE RAW Emf DATA ARE FROM THE FILE: 10171720 THE POWER SETTING PER CHIP WAS: 1.1 W THE DISTANCE TO THE FRONT WALL WAS 30 MM

CHIP ONET(N) Tavg-Is Nul Nu2

- 1 1.08 16.00 44.33 20.74 FLUX BASED RAYLEICH NUMBER * E-9 IS: 3.93 AVERAGE TEMPERATURE: 26.089 SINK TEMPERATURE: 10.085
- 2 1.09 15.48 46.12 21.58 FLUX RASED RAYLEIGH NUMBER * E-9 IS: 3.94 AVERAGE TEMPERATURE: 25.562 SINK TEMPERATURE: 10.085
- 3 1.10 15.83 42.84 20.04 FLUX BASED RAYLEJGH NUMBER * E-9 IS: 4.03 AVERAGE TEMPERATURE: 26.917 SINK TEMPERATURE: 10.085
- 4 1.09 16.05 44.67 20.90 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 3.98 AVERAGE IEMPERATURE: 26.136 SINK IEMPERATURE: 10.085
- 5 1.10 17.57 40.98 19.17 FLUX BASED RAYLEIGH NUMPER * E-3 IS: 4.06 AVERAGE TEMPERATURE: 27.657 .SINK TEMPERATURE: 10.085
- 6 1.10 16.42 44.03 20.50 FLUX BASED RAYLEJGH NUMBER ★ E-9 IS: 4.03 AVERAGE TEMPERATURE: 26.509 SINK TEMPERATURE: 10.085
- 7 1.10 15.60 46.18 21.60 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 3.98 AVERAGE TEMPERATURE: 25.688 SINK TEMPERATURE: 10.085
- 8 1.10 16.43 43.88 20.53 FLUX BASED RAYLEJGH NUMPRER * E-9 IS: 4.02 AVERAGE TEMPERATURE: 26.519 SINK TEMPERATURE: 10.085
- 9 1.10 15.63 46.12 21.58 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 3.98 AVERAGE TEMPERATURE: 25.717 SINK TEMPERATURE: 10.085

REDUCED DATA FOR INPUT POWER 1.5 W CHAMBER WIDTH = 30 mm

THE RAW Emf DATA ARE FROM THE FILE: 10211130 THE FOWER SETTING PER CHIP WAS: 1.5 $\rm H$ THE DISTANCE TO THE FRONT WALL WAS 30 MM

CHIP QNET(W) Tavg-Ts Nut Nu2

- 1 1.52 22.39 44.65 20.89 FLUX BAGED RAYLEJGH NUMPER * E-9 IS: 5.94 AVERAGE TEMPERATURE: 32.569 SINK TEMPERATURE: 10.180
- 2 1.53 21.80 46.10 21.57 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 5.94 AVERAGE TEMPERATURE: 31.978 SINK TEMPERATURE: 10.180
- 3 1.54 24.07 42.22 19.75 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 6.15 AVERAGE IEMPERATURE: 34.252 SINK IEMPERATURE: 10.180
- 4 1.54 22.27 45.37 21.23 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 6.00 AVERAGE TEMPERATURE: 32.450 SINK TEMPERATURE: 10.180
- 5 1.54 23.39 43.35 20.28 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 6.09 AVERAGE TEMPERATURE: 33.574 SINK TEMPERATURE: 10.180
- 6 1.55 22.61 45.06 21.08 FLUX BASED RAYLEIGH NUMBER ★ E-9 IS: 6.07 AVERAGE IEMPERATURE: 32.788 SINK TEMPERATURE: 10.180
- 7 1.54 21.66 46.86 21.92* FLUX BASED RAYLEJGH NUMBER * E-9 IS: 5.93 AVERAGE IEMPERATURE: 31.837 SINK TEMPERATURE: 10.180
- 8 1.54 22.30 45.54 21.30 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 6.03 AVERAGE TEMPERATURE: 32.482 SINK TEMPERATURE: 10.180
- 9 1.54 20.60 49.26 23.05 FLUX BASED RAYLEJGH NUMBER * E-9 IS: 5.92 AVERAGE TEMPERATURE: 30.782 SINK TEMPERATURE: 10.180

REDUCED DATA FOR INPUT POWER 2.5 wCHAMBER WIDTH = 30 mm

THE RAN Emf DATA ARE FROM THE FILE: 10182338 THE POWER SETTING PER CHIP NAS: 2.5 $\rm M$ THE DISTANCE TO THE FRONT WALL WAS 30 MM

CHIP ONET(W) Tavg-Is Nul Nu2

1 2.44 31.61 51.08 23.90 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 10.54 AVERAGE TEMPERATURE: 41.698 SINK TEMPERATURE: 10.087

- 2 2.45 30.24 53.65 25.10 FLUX BASED RAYLEJGH NUMBER * E-9 IS: 10.44 AVERAGE TEMPERATURE: 40.331 SINK TEMPERATURE: 10.087
- 3 2.48 33.03 49.69 23.25 FLUX BASED RAYLEJGH NUMBER * E-9 IS: 10.86 AVERAGE TEMPERATURE: 43.113 SINK TEMPERATURE: 10.087
- 4 2.46 31.27 52.14 24.39 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 10.60 AVERAGE TEMPERATURE: 41.356 SINK TEMPERATURE: 10.087
- 5 2.47 32.19 50.86 23.79 FLUX BASED RAYLEIGH NUMBER ★ E-9 IS: 10.74 AVERAGE 1EMPERATURE: 42.277 SINK TEMPERATURE: 10.087
- 6 2.49 31.14 52.84 24.72 FLUX BASED RAYLEJGH NUMBER * E-9 IS: 10.68 AVERAGE TEMPERATURE: 41.225 SINK TEMPERATURE: 10.087
- 7 2.48 30.10 54.39 25.44 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 10.52 AVERAGE TEMPERATURE: 40.189 SINK TEMPERATURE: 10.087
- 8 2.48 30.94 52.97 24.78 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 10.62 AVERAGE TEMPERATURE: 41.023 SINK TEMPERATURE: 10.087
- 9 2.48 28.94 56.51 26.44 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 10.39 AVERAGE TEMPERATURE: 39.028 SINK TEMPERATURE: 10.087

REDUCED DATA FOR INPUT POWER 3.0 W CHAMBER WIDTH = 30 mm

THE RAW Emf DATA ARE FROM THE FILE: 10191310 THE POWER SETTING PER CHIP WAS: 3.0 H THE DISTANCE TO THE FROM WALL WAS 30 MM

CHIP QNET(N) Tavg-Ts Nut Nu2

- 1 2.96 38.29 51.36 24.03 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 13.73 AVERAGE TEMPERATURE: 48.440 SINK TEMPERATURE: 10.154
- 2 2.98 36.50 54.14 25.33 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 13.56 AVERAGE TEMPERATURE: 46.657 SINK TEMPERATURE: 10.154
- 3 3.01 38.80 51.50 24.10 FLUX BASED RAYLEJGH NUMBER * E-9 IS: 14.03 AVERAGE TEMPERATURE: 48.959 SINK IEMPERATURE: 10.154
- 4 2.99 38.03 52.27 24.46 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 13.85 AVERAGE TEMPERATURE: 48.185 SINK TEMPERATURE: 10.154
- 5 3.00 38.62 51.66 24.17 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 13.98 AVERAGE TEMPERATURE: 48.777 SINK TEMPERATURE: 10.154
- 6 3.02 36.60 54.74 25.61 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 13.76 AVERAGE TEMPERATURE: 46.755 SINK TEMPERATURE: 10.154
- 7 3.01 36.49 54.71 25.60[°] FLUX BASED RAYLEIGH NUMBER * E-9 IS: 13.69 AVERAGE TEMPERATURE: 46.642 SINK TEMPERATURE: 10.154
- 8 3.01 36.62 54.55 25.52 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 13.72 AVERAGE TEMPERATURE: 46.771 SINK TEMPERATURE: 10.154
- 9 3.01 33.27 59.88 28.01 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 13.23 AVERAGE TEMPERATURE: 43.421 SINK TEMPERATURE: 10.154

TEMPERATURE DATA FOR INPUT POWER 0.1 W CHAMBER WIDTH = 9 mm

RESULTS ARE STORED IN FILE: 11050029

EXPERIMENT CARRIED AMBIENT TEMP (CELS	OUT AT IUS) OF:	22.78		
BATH TEMP : 10 TEMPERATURE READIN	C GS IN DEGREE	ES_CELSI	US	DACK
CHIP NO1: 14.34 14.2	5 14.16	14.24	14.08	14.40
CHIP NO2: 14.48 14.3	3 14.32	14.32	14.22	14.54
CHIP NO3: 14.58 14.5	3 14.49	14.48	14.54	14.64
CHIP NO4: 14.39 14.2	5 14.10	14.12	14.02	14.45
CHIP NO5: 14.43 15.8	9 14.33	14.37	14.26	14.49
CHIP NO6: 14.65 14.3	7 00.00	14.24	14.58	14.71
CHIP N07: 14.13 14.1	4 14.19	14.17	14.08	14.19
CHIP N08: 14.59 14.4	1 14.42	00.00	14.24	14.65
CHIP N09: 14.71 14.2 POWER (WATTS):	.099 8 16.01 .099	16.01	14.45	14.77
HEAT EXCHANGERS IE BOTTOM: TOP:	MFERATURES:	RIGHT 09.914 10.011	CENTER 09.967 00.000	LEFT 09.965 10.392
BACK PLANE TEMPERA T(55): 12.97 T(55): 13.12 T(74): 13.52 T(75): 13.83 T(76): 13.99 T(77): 13.25	TURES :		1 T	
SOURCE VOLTAGE: 1	.219			
VOLTAGE TO THE HEA CHIP #1:	TERS :			

TEMPERATURE DATA FOR INPUT POWER 0.7 W CHAMBER WIDTH = 9 mm

RESULTS ARE STORED IN FILE: 11062057

EXPERIMENT CARRIED OUT AT AMBIENT TEMP (CELSIUS) OF:	20.61		
TEMPERATURE READINGS IN DEGREE	S CELSI	115	
CENTER TOP RIGHT CHIP NO1: 23.48 23.27 22.85	LEFT 23.21	BOTTOM 21.49	BACK 23.88
POWER (WAITS): .696 CHIP NO2: 24.85 23.75 23.74	23.74	23.07	25.26
PUNER (NATIS): .701 CHIP N03: 24.78 24.57 24.32	23.70	24.51	25.19
CHIP N04: 23.92 22.97 22.82	22.78	21.97	24.32
CHIP N05: 24.77 23.82 24.12 POWER (WAIIS):	24.42	23.69	25.17
CHIP NO6: 25,92 23,76 00.00 POWER (WAILS): .709	23.15	25,35	26.33
CHIP NO7: 23.12 22.57 23.13 POWER (WAITS): .707	22.84	21.02	23.53
CHIP N08: 24.84 23.90 23.94 POWER (WATTS): .707	00.00	22.83	25.25
CHIP NO9: 25.78 22.75 19.26 POWER (WATTS): .706	23.34	24.30	26.19
HEAT EXCHANGERS TEMPERATURES: BOTTOM: TOP:	RIGHT 09.972 10.047	CENTER 10.070 00.000	LEF1 10.088 10.137
BACK PLANE TEMPERATURES : T(55): 15.17 T(56): 15.45 T(74): 15.92 T(75): 15.99 T(75): 16.29 T(77): 15.68		τ	
SOURCE VOLIAGE: 3.259			
VULIAGE 10 THE HEATERS : CHIP #1: 2.587 CHIP #2: 2.731 CHIP #3: 2.720 CHIP #3: 2.722 CHIP #5: 2.575 CHIP #5: 2.575 CHIP #6: 2.718 CHIP #7: 2.718 CHIP #8: 2.718 CHIP #8: 2.718			

TEMPERATURE DATA FOR INPUT POWER 1.1 W CHAMBER WIDTH = 9 mm

RESULTS ARE STORED IN FILE: 11022255 EXPERIMENT CARRIED DUT AT AMBIENT TEMP (CELSIUS) OF: 21.11 BATH TEMP : 10 C TEMPERATURE READINGS IN DEGREES CELSIUS CENTER RIGHT IFFT BOITOM TOP BACK CHIP NO1: 28.92 28.61 POWER (WATTS): 1.093 28.26 28.57 25.77 29.87 CHIP NO2: 31.27 29.86 POWER (WAITS): 1.100 29,60 29.60 28.52 29.97 CHIP N03: 30.49 30.42 3 POWER (WAITS): 1.1071 30.02 28,65 30.37 30.08 CHIP N04: 29.63 28.45 28.11 26.78 30.04 27.89 POWER (WATTS): 1.104 CHIP ND5: 31.16 29.79 30.20 POWER (WATTS): 1.107 29.54 30.63 30.08 CHIP NO6: 31.91 28.89 (POWER (WAITS): 1.114 00.00 28.72 31.17 30.18 CHIP N07: 28.48 27.51 28,46 28.34 25.07 30.15 POWER (WATTS): 1.112 CHIP NO8: 31.20 30.08 POWER (WATTS): 1.111 30.00 00.00 28.01 30.14 CHIP ND9: 32.68 28.26 31.03 31.03 30.57 30.11 POWER (WATTS): 1.110 HEAT EXCHANGERS TEMPERATURES: RIGHT CENTER FEFT BOTTOM: 09.839 10.128 10.241 TOP: 09.863 00.000 09.952 BACK PLANE TEMPERATURES : T(55): 17.38 1(56): 17.58 T(74): 18.00 I(75): 18.02 T(76): 18.41 1(77): 17.63 ٠ SOURCE VOLTAGE: 4,086 VOLTAGE TO THE HEATERS : 3.244 CHIP #1: CHIP #2: 3.425 CHIP #3: 3.411 CHIP #4: 3,413 CHIP #5: 3.229 CHIP #6: 3.406 CHIP #7: 3.407 CHIP #8: 3.408 CHIP #9: 3.409

TEMPERATURE DATA FOR INPUT POWER 1.5 W CHAMBER WIDTH = 9 mm

RESULTS ARE STORED IN FILE: 11091225

EXPERIMENT CARRIED OUT AT AMBIENT TEMP (CELSIUS) OF: BATH TEMP : 10 C	21.83		
TEMPERATURE READINGS IN DEGREN CENTER TOP RIGHT CHIP NO1: 36.71 36.38 35.78	ES CELSIU LEFT 1 36,25	JS BOTTOM 32,76	BACK 37.56
POWER (WAITS): 1.489 CHIP NO2: 38.97 36.79 37.06 POWER (WAITS): 1.497	37.06	35.88	39.83
CHIP ND3: 38.33 37.92 37.67 POWER (WATTS): 1.5093 CHIP_ND4: 37.06 35.37 35.16	34.98 34.59	37.83 33.41	39.20 37.92
POWER (HAITS): 1.504 CHIP NOS: 38.29 36.57 37.19 POWER (HAITS): 1.508	37.75	36.20	39.16
CHIP N06: 39.40 35.38 00.00 POWER (HATTS): 1.516 CHIP N07: 34.94 33.67 35.04	34.97 34.46	38.23 30.18	40.27 35.81
PUNER (NHITS): 1.512 CHIP N08: 38.18 35.83 36.98 POWER (HATTS): 1.512	00.00	34.50	39.05
POWER (WAITS): 1.511	36.52	36.03	40.58
BOITOM: TOP:	09.828	09.977	10.040
BACK PLANE TEMPERATURES : T(55): 20.82 T(55): 21.73 T(74): 22.48 T(75): 22.33 T(75): 22.64 T(77): 21.31		٢	
SOURCE VOLTAGE: 4.771			
VOLTAGE TO THE HEATERS : CHIP #1: 3.789 CHIP #2: 4.000 CHIP #3: 3.983 CHIP #4: 3.987 CHIP #4: 3.987 CHIP #5: 3.772 CHIP #5: 3.979 CHIP #7: 3.981 CHIP #8: 3.982 CHIP #9: 3.983			

TEMPERATURE DATA FOR INPUT POWER 2.5 W CHAMBER WIDTH = 9 mm

RESULTS ARE STORED IN FILE: 11082020

EXPER AMBIE BATH	IMENT CAR NT TEMP (TEMP :	RIED OUT CELSIUS) 10 C	AI OF:	21.28		
TEMPER	CENTER 46.62	ADINGS 1 TOP 45.93	N DEGREE RIGHT 45.41	ES CELSIN LEFT 1 46.08	JS BOTTOM 40.22	BACK 48.05
CHIP NO2:	50.04	46.15	47.23	47.23	43.85	51.48
CHIP NO3:	(WATTS): 48.91	2.520	48.04	45.63	48.30	50.37
CHIP NO4:	(WATTS): 47.00	2,538 43,52	8 44.22	42.84	41.35	48.45
POWER CHIP NO5:	(WATTS): 48.77	2.531 46.61	47.23	48,29	45.89	50.23
POHER CHIP NOS:	(WATTS):	2.538	0.0.00	44.08	48.13	51.45
- POWER	(WATTS):	2,552	42.55	42.59	25 62	44 92
POWER	(WATTS):	2.544	43.65	42.63	35.63	44.02
CHIP NO8: POWER	48.86 (WAITS):	45.42 2.544	47.09	00.00	43.17	50.32
CHIP NU9: POWER	49.89 (WATTS):	42.54 2.541	34.29	45.52	45.93	51.35
HEAT E	EXCHANGER BOTTOM: FOP:	S TEMPER	ATURES:	RIGHT 09.859 09.803	CENIER 10.037 00.000	LEF (10.110 10.073
BACK F T(55) T(56) T(74) T(75) T(76) T(77)	PLANE TEM 22.95 24.01 24.80 24.59 24.97 23.67	PERATURE	S :		5	
SOURCE	VOL TAGE	6.193				
VOLTAC CHIP 4 CHIP 4 CHIP 4 CHIP 4 CHIP 4 CHIP 4 CHIP 4 CHIP 4	GE TO THE 1: 4, 2: 5, 4: 5, 5: 4, 5: 4, 6: 5, 7: 5, 8: 7, 8: 7,	HEATERS 921 193 172 176 397 165 169 169 171	:			

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TEMPERATURE DATA FOR INPUT POWER 3.0 W CHAMBER WIDTH = 9 mm

RESULTS ARE STORED IN FILE: 11072058

EXPERIMENT CARRIED OUT AT AMBIENT TEMP (CELSIUS) OF: BATH TEMP : 10 C	21.00		
 TEMPERATURE READINGS IN DEGREE TEMPERATURE READINGS IN DEGREE CHIP NO1: 55.97 54.46 55.08 POHER (HATI5): 2.938 CHIP NO2: 61.12 57.34 58.19 POHER (HATI5): 2.957 CHIP NO3: 58.47 58.54 57.89 POHER (HATI5): 2.957 CHIP NO4: 57.35 53.68 54.52 POHER (HATI5): 2.965 CHIP NO5: 58.98 57.68 58.44 POHER (HATI5): 2.993 CHIP NO7: 52.97 51.59 POHER (HATI5): 2.993 CHIP NO7: 52.97 51.59 POHER (HATI5): 2.993 CHIP NO7: 52.97 57.20 59.10 POHER (HATI5): 2.984 	S CELSI LEFT 1 55.59 58.19 55.35 54.33 59.12 55.89 53.26 00.00 56.95	JS 30 T T OH 45.61 54.57 58.30 49.46 56.79 59.33 43.41 54.97 56.66	BACK 57.66 62.82 60.18 59.05 60.69 62.89 54.68 62.28 62.17
HEAT EXCHANGERS TEMPERATURES: BOTTON: TOP:	RIGH1 09.783 09.816	CENTER 10.022 00.000	LEFT 10.176 10.063
BACK PLANE TEMPERATURES : T(55): 32.35 T(56): 34.45 T(74): 35.59 T(75): 35.08 T(75): 35.20 T(77): 33.52 SOURCE VOLTAGE: 6.715		1 T	
VOLIAGE TO THE HEATERS : CHIP #1: 5.339 CHIP #2: 5.633 CHIP #3: 5.611 CHIP #4: 5.615 CHIP #5: 5.314 CHIP #6: 5.603 CHIP #7: 5.608 CHIP #8: 5.607 CHIP #9: 5.608			

REDUCED DATA FOR INPUT POWER 0.1 W CHAMBER WIDTH = 9 mm

THE RAW Emf DATA ARE FROM THE FILE: 11050029 THE POWER SETTING PER CHIP WAS: 0.1 W THE DISTANCE TO THE FRONT WALL WAS 9 MM

CHIP QNET(N) Tava-Ta No 1 Mu2 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 1 . 30 AVERAGE TEMPERATURE: 14.242 SINK TEMPERATURE: 10,139 FLUX BASED RAYLEIGH NUMBER * E-9 IS: .31 AVERAGE TEMPERATURE: 14.221 SINK TEMPERATURE: 10,139 .10 4.39 14.43 6 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 3 6.75 .31 AVERAGE TEMPERATURE: 14.525 SINK TEMPERATURE: 10.139 4.07 15.54 .10 7.27 FLUX BASED RAYLEIGH NUMBER * E-9 IS: .31 AVERAGE TEMPERATURE: 14,208 SINK TEMPERATURE: 10.139 4.36 14.52 5 .10 6.80 FLUX BASED RAYLEIGH NUMBER * E-9 IS: .31 AVERAGE TEMPERATURE: 14,497 SINK TEMPERATURE: 10.139 .10 4.33 14.70 6 6.88 FLUX BASED RAYLEIGH NUMBER * E-9 IS: .31 AVERAGE TEMPERATURE: 14,473 SINK TEMPERATURE: 10.139

- 7 .10 4.01 15.R6 7.42 FLUX BASED RAYLEIGH NUMRER * E-9 IS: .31 AVERAGE TEMPERATURE: 14.153 SINK TEMPERATURE: 10.139
- 8 .10 4.33 14.67 6.86 FLUX BASED RAYLEIGH NUMBER * E-9 IS: .31 AVERAGE TEMPERATURE: 14.471 SINK TEMPERATURE: 10.139
- 9 .10 4.52 14.00 6.55 FLUX DASED RAYLEIGH NUMRER * E-9 IS: .31 AVERAGE IEMPERATURE: 14.660 SINK TEMPERATURE: 10.139

REDUCED DATA FOR INPUT POWER 0.7 W CHAMBER WIDTH = 9 mm

THE RAN Emp DATA ARE FROM THE FILE: 11062057 THE POWER SETTING PER CHIP WAS: 0.7 $\rm M$ THE DISTANCE TO THE FROMT WALL WAS 9 MM

CHIP ONET(W) Tavg-Ts Nut Nu2

1 .68 13.03 34.38 16.08 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 2.41 AVERAGE TEMPERATURE: 23.174 SINK TEMPERATURE: 10.145

- 2 .69 13.11 34.42 16.10 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 2.43 AVERAGE TEMPERATURE: 23.251 SINK TEMPERATURE: 10.145
- 3 .69 14.31 31.75 14.86 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 2.48 AVERAGE TEMPERATURE: 24.456 SINK TEMPERATURE: 10.145
- 4 .69 13.07 34.63 16.20 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 2.44 AVERAGE TEMPERATURE: 23.219 SINK TEMPERATURE: 10.145
- 5 .69 14.31 31.75 14.86 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 2.48 AVERAGE IEMPERATURE: 24.451 SINK IEMPERATURE: 10.145
- 6 .70 14.65 31.20 14.60 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 2.50 AVERAGE TEMPERATURE: 24.794 SINK TEMPERATURE: 10.145
- 7 .70 12.79 35.62 16.66 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 2.44 AVERAGE IEMPERATURE: 22.933 SINK TEMPERATURE: 10.145
- 8 .70 14.17 32.16 15.04 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 2.48 AVERAGE IEMPERATURE: 24.313 SINK TEMPERATURE: 10.145
- 9 .69 13.12 34.64 16.21 FLUX BASED RAYLEJGH NUMBRER * E-9 IS: 2.45 AVERAGE TEMPERATURE: 23.266 SINK TEMPERATURE: 10.145

REDUCED DATA FOR INPUT POWER 1.1 W CHAMBER WIDTH = 9 mm

THE RAN Emf DATA ARE FROM THE FILE: 11022255 THE FOHER SETTING PER CHIP HAS: 1.1 H THE DISTANCE TO THE FRONT WALL WAS 9 MM

CHIP ONET(W) Tavg-Ts Nu1 Nu2

- 1 1.08 18.18 38.87 18.19 FLUX BASED RAYLEJGH NUMBER * E-9 IS: 4.02 AVERAGE TEMPERATURE: 28.377 SINK TEMPERATURE: 10.193
- 2 1.08 18.63 38.19 17.87 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 4.07 AVERAGE TEMPERATURE: 28.825 SINK TEMPERATURE: 10.193
- 3 1.09 19.71 36.38 17.02 FLUX BASED RAYLEIGH NUMBER • E-9 IS: 4.14 AVERAGE TEMPERATURE: 29.838 SINK TEMPERATURE: 10.133
- 4 1.09 18.29 33.06 18.28 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 4.07 AVERAGE TEMPERATURE: 28.480 SINK TEMPERATURE: 10.133
- 5 1.09 20.35 35.26 16.49 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 4.17 AVERAGE TEMPERATURE: 30.538 SINK TEMPERATURE: 10.193
- 6 1.10 20.24 35.66 16.68 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 4.19 AVERAGE TEMPERATURE: 30.429 SINK TEMPERATURE: 10.193
- 7 1.10 17.88 40.23 18.82 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 4.08 AVERAGE TEMPERATURE: 28.075 f SINK TEMPERATURE: 10.193
- 8 1.10 20.13 35.76 16.73 FLUX BASED RAYLEJGH NUMBER * E-9 IS: 4.18 AVERAGE TEMPERATURE: 30.321 SINK TEMPERATURE: 10.193
- 9 1.09 19.19 37.43 17.51 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 4.13 AVERAGE TEMPERATURE: 29.382 SINK TEMPERATURE: 10.193

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REDUCED DATA FOR INPUT POWER 1.5 W CHAMBER WIDTH = 9 mm

THE RAN Emf DATA ARE FROM THE FILE: 11091225 THE POWER SETTING PER CHIP WAS: 1,5 H THE DISTANCE TO THE FRONT WALL WAS 9 MH

CHIP QNET(W) Tavg-Ts Nu1 Nu2

1 1.47 25.92 37.30 17.45 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 5.96 AVERAGE TEMPERATURE: 26.108 SINK IEMPERATURE: 10.186

- 2 1.47 25.87 37.60 17.59 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 6.00 AVERAGE TEMPERATURE: 36.053 SINK TEMPERATURE: 10.186
- 3 1.49 27.17 36.12 16.90 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 6.13 AVERAGE TEMPERATURE: 37.353 SINK TEMPERATURE: 10.186
- 4 1.48 25.44 38.39 17.96 FLUX BASED RAYLEJGH NUMBER * E-9 IS: 5.99 AVERAGE TEMPERATURE: 35.625 SINK TEMPERATURE: 10.186
- 5 1.49 27.48 35.69 16.70 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 6.15 AVERAGE IEMPERATURE: 37.664 SINK TEMPERATURE: 10.186
- 6 1.49 27.26 36.16 16.92 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 6.17 AVERAGE TEMPERATURE: 37.450 SINK TEMPERATURE: 10.186
- 7 1.49 24.25 40.46 18.93 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 5.95 AVERAGE TEMPERATURE: 34.440 SINK TEMPERATURE: 10.185
- 8 1.49 27.02 36.36 17.01 FLUX BASED RAYLEJGH NUMBER * E-9 IS: 6.13 AVERAGE TEMPERATURE: 37.211 SINK TEMPERATURE: 10.186
- 9 1.49 25.41 38.61 18.07 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 6.02 AVERAGE IEMPERATURE: 35.592 SINK TEMPERATURE: 10.186

REDUCED DATA FOR INPUT POWER 2.5 W CHAMBER WIDTH = 9 mm

THE RAW Emf DATA ARE FROM THE FILE: 11082020 THE POWER SETTING PER CHIP WAS: 2.5 W THE DISTANCE TO THE FRONT WALL WAS 9 MM

CHIP QNET(W) Tavg-Is Nut Nu2

- 1 2.47 35.42 46.27 21.65 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 11.15 AVERAGE TEMPERATURE: 45.692 SINK TEMPERATURE: 10.271
- 2 2.49 35.23 46.82 21.90 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 11.20 AVERAGE TEMPERATURE: 45.503 SINK TEMPERATURE: 10.271
- 3 2.50 37.64 44.23 20.69 FLUX BASED RAYLEJGH NUMBER * E-9 IS: 11.58 AVERAGE TEMPERATURE: 47.908 SINK TEMPERATURE: 10.271
- 4 2.50 34.33 48.22 22.56 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 11.14 AVERAGE TEMPERATURE: 44.605 SINK TEMPERATURE: 10.271
- 5 2.50 37.68 44.17 20.66 FLUX BASED RAYLEJGH NUMBER * E-9 IS: 11.58 AVERAGE TEMPERATURE: 47.946 SINK TEMPERATURE: 10.271
- 6 2.52 37.02 45.18 21.14 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 11.56 AVERAGE TEMPERATURE: 47.287 SINK TEMPERATURE: 10.271
- 7 2.51 32.27 51.53 24.11 FLUX BASED RAYLEJGH NUMBER * E-9 IS: 10.96 AVERAGE TEMPERATURE: 42.536 SINK TEMPERATURE: 10.271
- 8 2.51 37.08 44.97 21.04 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 11.53 AVERAGE TEMPERATURE: 47.355 SINK TEMPERATURE: 10.271
- 9 2.51 33.79 49.19 23.01 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 11.12 AVERAGE TEMPERATURE: 44.057 SINK TEMPERATURE: 10.271

REDUCED DATA FOR INPUT POWER 3.0 W CHAMBER WIDTH = 9 mm

THE RAW EMF DATA ARE FROM THE FILE: 11072058 THE POWER SETTING PER CHIP WAS: 3.0 W THE DISTANCE TO THE FRONT WALL WAS 9 MM

CHIP QNET(W) Tavg-Is Nul Nu2

1 2.90 44.40 43.64 20.42 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 14.41 AVERAGE IEMPERATURE: 54.762 SINK TEMPERATURE: 10.362

- 2 2.92 46.34 42.14 19.72 FLUX BASED RAYLLIGH NUMBER * E-9 IS: 14.79 AVERAGE TEMPERATURE: 56.697 SINK TEMPERATURE: 10.362
- 3 2.94 47.28 41.61 19.47 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 15.04 AVERAGE IEMPERATURE: 57.639 SINK TEMPERATURE: 10.362
- 4 2.93 44.68 43.84 20.51 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 14.61 AVERAGE TEMPERATURE: 55.040 SINK TEMPERATURE: 10.362
- 5 2.94 48.33 40.74 19.06 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 15.20 AVERAGE TEMPERATURE: 58.691 SINK TEMPERATURE: 10.362
- 6 2.96 48.31 40.97 19.17 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 15.28 AVERAGE TEMPERATURE: 58.676 SINK TEMPERATURE: 10.362
- 7 2.95 42.01 46.78 21.89 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 14.29 AVERAGE TEMPERATURE: 52.372 SINK TEMPERATURE: 10.362
- 8 2.95 48.82 40.44 18.92 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 15.31 AVERAGE IEMPERATURE: 59.183 SINK TEMPERATURE: 10.362
- 9 2.95 44.89 43.86 20.52 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 14.71 AVERAGE IEMPERATURE: 55.253 SINK IEMPERATURE: 10.362

APPENDIX D

SOFTWARE LISTING

PROGRAM CalcDiel ******** 20 23 23 30 31 ! EDITED BY LT E. TORRES. FROM URIGINALS OF ! PAMUK [REF.12] AND BENEDICT [REF. 13] I THIS PROGRAM ANALYSES THE DATA READ FROM + I A DATA FILE DESIGNATED BY THE OPERATOR.IT+ REDUCES THE DATA TO CALCULATIONS OF HEI + POWER. RAYLEIGH NUMBER AND MUSELT NUMBER. 50 90 VARIABLES USED ARE : I EMF : VOLTARE FROM THE THERMOCOUPLES. POWER : POWER DISSIPATED BY THE HEATERS. I T(1) : TEMPERATURE CONVERTED FROM THERMOCOU-96 97 PLES VOLTAGE. TAVG : IS THE AVERAGE TEMPERATURE OF THE CHIP. IT IS OBTAINED MULTIPLYING THE TEMPERATURE FOUND IN EACH FACE BY THE AREA AND DIVIDING BY THE TO-38 BY THE AREA AND DIVIDING BY THE TU-TAL AREA. Is : CHIP BACK SURFACE TEMPERATURE. Itim: ILM TEMPERATURE OF THE FC-75. UNET : SLECTRIC POWER MINUS CONDUCTION LOSSES. UNET : SLECTRIC POWER MINUS CONDUCTION LOSSES ISINK: AVEFACE OF THE 6 THERMOCOUPLES IN THE UPPER AND LOWER HEAT-EXCHANCERS. NUT : VERTICAL LENGTH BASED NUSSELT NUMBER NUT : REA-PERIMETER BASED NUSSELT NUMBER. STUED UNDELDIES OF SLEF FYEM HANDRES. ! OTHER VARIABLES ARE SELF EXPLANATORIES. COM /Co/ D(7) DIM Emi(76), Power(3), T(76), Tavg(9), Ts(3) DIM TH:1m(9).Onet(9).H(9).k(9).Rho(9).Cp(9) DIM N(9), Nu(9), Ra(9), Delt(9), Alta(9), Pr(9) DIM Gr(9), Beta(9), Dpow(9), Dts(9), Rp(8) 1 CORRELATION FACTORS TO CONVERT Emt TO DECREES CELSIUS. DATA 0.10086091.25727.9.-767345.8.78025596. DATA -9247496589.6.30E11.-2.66E13.3.34ET4 DATA 2.50.2.06.2.08.2.50.2.08.2.08.2.08.2.08 200 210 220 250 270 280 PEAD DIAL READ Rp(+) PRINTER IS 701 BEEP BEEP 290 300 INPUT "ENTER THE NAME OF THE FILE CONTAINING DATA".Oldfile\$ PRINT USING "10X, "THE RAW Emf DATA ARE FROM THE FILE: "".10A":01dfiles INPUT "ENTER THE POWER SETTING ". Power\$

PRINT USING "9X."" THE POWER SETTING PER CHIP GAS: "". DA":PowerS 340 341 FRINT USING "TOX." THE DISTANCE TO THE FRONT WALL WAS 9 MM """ 344 350 370 PRINT 380 BEEF 390 BEEP ASSIGN @File TO Oldfile\$ 400 401 ENTER @File:Emf(+) 410 420 I CONVERT Emf TO DEGREES CELSIUS ... 430 431 43 440 FOR I=0 TO 60 45.0 Sum=0 460 FOR J=0 TO 7 470 Sum=Sum+D(J)+Emf(I)'J 480 NEXT J 490 T(I)=Sum 500 NEXT I 502 FOR I=71 TO 76 Sum=1) 504 FOR J=0 TO 7 506 Sum*Sum+D(J)+Emf(D))J 508 NEXT J 509 T(I)=Sum 510 511 513 520 CONVERT Emf TO POWER * 521 522 530 ! ******************** 1=1 Volt=Emf(61) FOR 1-62 TO 70 Power(J)=Emf(I)+(Volt-Emf(I))/Rp(I-62) 560 i=.1+1 NEXT I 1 144444444 I AREA OF THE BLOCK FACES + 1 *************************** 612 520 630 Acen=1.92E-4 Alei=1.44E-4 Aria=1.44E-4 640 Atco=4.3E-9 Hbot=4.3E-5 * 670 Ato+=5.76E-4 580 690 691 ICALCULATE THE AVERAGE TEMPERATURES OF THE BLOCK FACES + IF A THERMOCCUPLE IS FOUND OPENED.IT SHOULD BE TAKEN OFF.+ 700 701 210 Tavg(1)=(T(0)+Acen+T(1)+Atop+T(2)+Arig+T(3)+Alet+T(4)+Abot)/Atot Tavg(2)=(T(6)+Acen+T(7)+Atop+T(8)+Arig+T(9)+Alet+T(10)+Abot)/Atot

740 Tavg(4)=(T(18)*Acen+T(19)*Atop+T(20)*Arig+T(21)*Alef+T(22)*Abot)/Atot lavg14)*[(13)*keen*[(13)*kop*[(25)*k1op*[(25)*k1op*[(27)*k1e]*f(28)*kbot)/Atot lavg(5)=(1(24)*keen*[(25)*k1op*[(25)*k1op*[(27)*k1e]*f(27)*k1e]*f(28)*kbot)/Atot lavg(7)=(1(36)*keen*f(37)*k1op*[(38)*k1op*[(38)*k1op*[(38)*k1op*](38)*kbot)/(ktot*f1e) lavg(7)=(1(36)*keen*f(37)*k1op*[(38)*k1op*[(38)*k1op*[(38)*k1op*](38)*kbot)/(ktot*f1e)) lavg(8)=(1(42)*keen*f(48)*k1op*[(44)*k1op*[(46)*kbot)/(ktot*f1e)) 760 780 Tavg(9)=(T(48)*Acen+T(49)*Atop+T(50)*Arig+T(51)*Alef+T(52)*Abot)/Atot 800 ! RESISTANCE OF PLEXIGLASS. FOUND WITH A CONDUCTIVITY OF * ! 0.195 H/m.K AND A LENGTH OF 19.5 MM. 852 853 860 Rc=520.83 890 ! CHIP BACK SURFACE TEMPERATURES . ! ******************************* 900 Ts(1)=T(5) Ts(2)=T(11) Ts(2)=T(17) Ts(4)=T(23) Ts(5)=T(29) 940 950 Ts(6)=T(35) $T_{S}(7) = T(41)$ 960 970 Ts(8)=T(47) 980 Ts(9)=T(53) Issum=) FOR J=1 TO 3 Issum=Issum+Is(J) 1020 NEXT J 1040 Tsavg=Tssum/3 1041 1060 ! CONDUCTION LOSS CALCULATION. * 1061 1062 010553=(T(17)-T(75))/Rc Qloss5=(T(29)-T(55))/Rc Dloss7=(T(41)-T(54))/Rc 10.90 Qloss=(Qloss3+0loss5+0loss7)/3 1120 I AVERAGE SINK TEMPERATURE CALCULATION * Isink=(T(57)+T(58)+T(59)+T(60)+T(71)+T(72))/6 TWO CHARACTERISTIC LENGTHS.WILL BE USED TOGALCULATE MUSSELT HUMBERS : I LI BASED IN THE VERITAL DIMENSION OF THE GRIP 7/24,MM AND LZ BASED IN THE SUMMITION OF THE GREASDIVIDED BY THE PERIMETER. 1154 * 1 = 2.40E - 2 1 =1161 I TO PRINT THE OUTPUT HEADINGS. * 1174 Nu2 "",10A" 1180 PRINT USING "9X,""CHIP ONET(W) Tavg-Ts Nul 1200 PRINT 1210

! CALCULATION OF NET POWER, Nu AND Ra. . 1220 1230 I ************ 1231 FOR J=1 TO 9 1250 1260 ! CALCULATION OF Onet 1270 Qnet(J)=Power(J)-Qloss 1300 CALCULATION OF Tfilm 1310 Tfilm(J)=(Tavg(J)+Tsink)/2 1340 ! CALCULATION OF A DELTA TEMPERATURE 1350 1370 Delt(J)=Tavg(J)-Tsink ! CALCULATION OF CONVECTION COEFFICIENT 1380 1390 H(J)=Qnet(J)/(Atot*Delt(J)) 1410 1420 ! CALCULATION OF FC-75 THERMAL CONDUCTIVITY. 1430 K(J)=(.65-7.89474E-4+Tfilm(J))/10 1440 1450 ! CALCULATION OF FC-75 DENSITY Rho(J)=(1.825-.00246*Tfilm(J))*1000 1460 1470 ! CALCULATION OF FC-75 SPECIFIC HEAT 1480 1490 Cp(J)=(.241111+3.7037E-4*Tfilm(J))+4180 1510 ! CALCULATION OF FC-75 VISCOSITY N(J)=1.4074-2.964E-2*Tfilm(J)+3.8018E-4*Tfilm(J)'2-2.7308E-6+Ttilm(J)'3+8. 1520 N(J)=1.4074-. 1679E-9+Tfilm(J)^4 1530 H(J)=N(J)+1.E-6 1540 1550 ! CALCULATION OF THE COEFFICIENT OF THERMAL 1551 ! EXPANSION [BETA] 1560 Beta(J)=.00246/(1.825-.00246*Tfilm(J)) 1570 1580 ! CALCULATION OF ALPHA 1590 Aifa(J)=K(J)/(Rho(J)*Cp(J)) 1600 1610 ! CALCULATION OF PRANDTL NUMBER. 1620 Pr(J)=N(J)/Alfa(J) 1630 1640 ! CALCULATION OF NUSSELT NUMBERS 1650 Nu1(J)=H(J)+L1/K(J) Hu2(J)=H(J)+L2/K(J) 1670 1710 ! CALCULATION OF GRASHOF NUMBER. Gr(J)=9.81*Beta(J)*(L1'3)*Del+(J)/N(J)'2 1720 1740 1750 ! CALCULATION OF RAYLEIGH NUMBER. 1760 Ra(J)=Gr(J)+Pr(J)+1.E-7 \$ 1780 1794 ! CALCULATION OF FLUX BASED RAYLEIGH NUMBER 1810 Raf(J)=((9.81*Beta(J)*L1*4*Onet(J))/(K(J)*N(J)*Al+a(J)*Ato+))*1.E-9 1830 1870 PRINT USING "10X.D.1X.5(5X.DD.DD.)"; J.Onet(J).Delt(J).Nu1(J).Nu2(J) 1880 1890 PRINT USING "12X.""FLUX BASED RAYLEIGH NUMBER + E-9 IS: "".DDD.DD":Rar(J) PRINT USING "12X.""AVERAGE TEMPERATURE:".DDD.DDD":Tavg(J) PRINT USING "12X.""SINK TEMPERATURE:".DDD.DDD":Tavg(J) 1930 1940

1960 NEXT J 1970 ASSIGN ⊕File TO + 1980 END

۲

1 ********************* 10 ! PROGRAM FASTSCAN + PROGRAM TO SCAN THE THREE UPPERMOST THERMOCOUPLES. I IT SCANS 3 CHANNELS FOR TEMPERATURE VARIATION MEASUREMENTS. 30 40 41 ! CHANNELS ARE 13,31 AND 49 50 50 Ipass=599 Pass=0 N=0 DIM T1(599).V1(2).Y1(599) 81 DIM T2(599),V2(2),Y2(599) DIM T3(599),V3(2),Y3(599) 82 90 CLEAR 709 CLEAR 72 1 ! THE THREE FILE NAMES THAT ARE REQUIRED FOLLOWING ! ARE TO STORE THE READINGS FROM THREE THERMOCOUPLES. 102 103 104 106 BEEP PRINTER IS 701 108 BEEP HPUT "ENTER THE FIRST FILE NAME: ".Newfile's IMPUT "ENTER THE SECOND FILE NAME: ".Newfile's INPUT "ENTER THE THAD FILE NAME: ".Newfile's INPUT "ENTER THE VOLTMETER READING: ".VS "RITH USTIME "ISX." RESULTS ARE STORED ON DISK "FASTSCAN' ".10A" 109 110 PRINT 114 116 PRINT USING "25X, ""FILE: "", 10A": Newfile15 PRINT 118 FRINT USING "25%, ""FILE: "".10A":Newfile2\$ 119 PRINT 120 FRINT USING "25X.""FILE: "".10A":Newfile3\$ PRINT WAIT 1 124 BEEP 125 OUTPUT 709: "AE1" WAIT 2 130 BEEP 140 OUTPUT 722: "T4 F1 R1 P0 Z0 ISTI S01 ISTN" 141 143 1 -----144 LOOP NUMBER ONE 145 146 ! START SCANNING CHANNEL # 13 + 147 ----OUTPUT 709: "AF13 AL13" 160 OUTPUT 709: "AS" BEEP 170 Timedatel*TIMEDATE 130 FOR Jj=0 TO Ipass OUTPUT 722:"T3" ENTER 722:V1(*) t 200 210 220 250 T1(Pass)=V1(1) Pass=Pass+1 251 N=N+1 260 NEXT JI Timedate2=TIMEDATE 263 DUTBUTINg2: #Amedate2-Timedate1

```
Pass=0
       ------
       I LOOP NUMBER TWO
       START SCANNING CHANNEL 31
       OUTPUT 709: "AF31 AL31"
       DUTPUT 709; "AS"
       FOR JJ=") TO lpass
OUTPUT 722:"T3"
ENTER 722:V2(+)
T2(Pacebolic)
         2(Pass)=V2(1)
       Pass=Pass+
       OUTPUT 722: "AC31"
       Pass=0
       LOOF NUMBER THREE +
                                   +
       ! START SCANNING CHANNEL 49 *
       1 ******************************
       OUTPUT 709: "AF49 AL49"
       DUTPUT 709: "AS"
       BEEP
       FOR JJ=0 TO Ipass
OUTPUT 722:"T3"
ENTER 722:V3(+)
       13(Pass)=V3(1)
       Pass=Pass+1
207
208
209
210
       NEXT JJ
       L END LOOPS
       PRINT USING "15x.""THE TOTAL TIME ELAPSED (SECONDS :"".2%. (DDD.DD)": fotal
t mel
       PRINT .
       PRINT USING 115%."TTHE TOTAL NUMBER OF SCANS : 11.2%. 0000.0.2% "IN
14
       FAINT USING "15%."THE VOLTMETER READING : 11.104.1:19
15
       BEENTER IS 1
G- 20 45 680 0-2
       I TRANSFER FIRST SLAN DATA
                                                                       5
       TRANSFERING THE SCAN DATA FROM CHANNEL 13
TO THE FILE. THIS FILE WILL BE USED. WITH
THE PROGRAM "PLOT". TO MAKE A PLOT OF TEM-
       PERALURE VS TIME.
       CREATE BDAT Newfile15.20
ASSIGN #File TO Newfile15
       OUTPUT #File:T1(+)
       FOR I1=0 TO Ipass
       T1(I1)=.10086091+25727.9+T1(I1)=757345.8+T1(I1):2+79002556+T1(I1):3
```

```
340
    NEXT II
341
     I TRANSFER SECOND SCAN DATA +
342
     344
     ITRANSFERING DATA FROM CHANNEL 31+
345
346
     ITO THE FILE
347
349
      CREATE BDAT Newfile23.20
350
351
     ASSIGN @File TO Newfile2$
OUTPUT @File:T2(+)
FOR I1=0 TO Ipass
352
353
     T2(I1)=,10086091+25727,9+12(I1)-767345,8+T2(I1)'2+78002556+T2(I1)'3 .
353
354
355
357
358
     NEXT II
             I TRANSFER THIRD SCAN DATA
359
     1+++++
360
     ! TRANSFERING DATA FROM CHANNEL 31 +
361
     ! TO THE FILE.
362
363
     CREATE BDAT Newfile35.20
ASSIGN #File TO Newfile35
OUTPUT #File:T3(+)
FOR Ii=0 TO Ipass
364
365
366
367
368
      T3(I1)=.10086091+25727.9+T3(I1)-767345.8+T3(I1)*2+78002556+T3(I1)*3
369
     NEXT II
390
     STOP
     EHD
400
```

5

1.0 ! FILE NAME: PLOT 20 40 50 ! THIS FROGRAM PLOTS THE DATA ACQUIRED BY 50 I PROGRAM "FASTSCAN", 30 PRINTER IS 705 90 BEEP Xmin=0 Xmax=200 120 BEEP INPUT "ENTER MINIMUM AND MAXIMUM Y-VALUES".Ymin.Ymax BEEP 140 Xstep=20 BEEP 160 Ystep=.2 130 BEEP PRINT "IN:SP1:IF 2000.2000.8000.7000:" 190 PRINT "SC 0.100.0.100;TL 2.0:" 200 210 5fx=100/(Xmax-Xmin) 220 Sfy=100/(Ymax-Ymin) PRINT "PU 0.0 PD" FOR Xa=Xmin TO Xmax STEP Xstep X=(Xa=Xmin)+Sfx PRINT "PA":X.".0: XT:" 240 250 260 270 280 290 NEXT Xa PRINT "PA 100.0:PU:" PRINT "PU PA 0.0 PD" 300 FOR Ya=Ymin TO Ymax SIEP Ystep Y=(Ya-Ymin)*Sfy PRINT "PA 0,":Y, "YT" NEXT Ya PRINT "PA 0.100 TL 0 2" FOR Xa=Xmin TO Xmax STEP Xstep 340 360 X=(Xa-Xmin)*Sfx PRINT "PA":X.".100: XT" NEXT Xa 390 PRINT "PA 100,100 PU PA 100.0 PD" FOR Ya=Ymin TO Ymax STEP Ystep 400 Y=(Ya-Ymin)+Sfy 420 PRINT "PD PA 100.".Y. "YT" NEXT Ya PRINT "PA 100.100 PU" PRINT "PA 0.-2 SR 1.5.2" FOR Xa=(min TO Xmax STEP Xstep) 430 440 450 460 470 X=(Xa=Xmin)*Six 1 480 PRINT "PA":X.".0:" PRINT "CP -2.-1:LB":Xa:"" 490 5 NEXT Ya PRINT "PU PA 0.0" FOR fa=fmin TO Ymax STEP Ystep IF ABS(Ya)<1.E-5 THEN Ya=0 Y=(Ya-Ymin)*Sfy 540 PRINT "PA 0.":Y."" PRINT "CP -5.-.25:LB";Ya;"" 560 NEXT Ya BEEP IF Idl=0 THEN

```
520
         Xlabel3="Time (sec)"
630
         BEEP
640
         YlabelS="Temperature (C)"
550
         PRINT "SR 1.5.2:PU PA 50.-10 CP":-LEN(Xiabel$)/2:"0:LB":Xiabei$:""
660
         PRINT "PA -11.50 CP 0, ";-LEN(Ylabel$)/2+5/6; "DI 0.1;LB": Ylabel$;""
670
        END IF
PRINT "CP 0.0"
630
        BEEP
700
         INPUT "ENTER THE NAME OF THE DATA FILE".D.file$
710
720
         ASSIGN @File TO D_file$
        BEEP
730
         Md=0
740
         BEEP
750
760
        Npairs=600
BEEP
770
        PRINTER IS 1
230
         Sym=1
        PPINIER IS 705
790
800
        PRINT "PU DI"
810
        IF Sym=1 THEN PRINT "SM."
IF Sym=2 THEN PRINT "SM+"
820
830
         IF Sym=3 THEN PRINT "SHo"
        IF Md>1 THEN
840
850
        FOR I=1 TO (Md-1)
360
        ENTER @File:Xa.Ya
370
        NEXT I
        END IF
890
        FOR Xa=0 TO 199 STEP .33333333
90.0
        ENTER MFile:Ya
910
        Ya=.10086091+25727.9+Ya-767345.8+Ya'2+78002556+Ya'3
920
930
        X=(Xa-Xmin)*Sfr
        Y=(Ya-Ymin)+Sfy
        IF Sym 3 THEN PRINT "SM"
IF Sym 4 THEN PRINT "SM"
PRINT "PA".x.Y."PD"
IF Sym 3 THEN PRINT "SR 1.2.1.6"
940
950
960
970
        IF Sym-4 THEN PRINT "WC2.4.39.0.-8.-4.0.0.5.4.0.:"

IF Sym-5 THEN PRINT "UC2.4.39.0.-8.-4.0.0.5.4.0.:"

IF Sym-5 THEN PRINT "UC0.0.39.-0.-6.-3.6.3.6.3.-6:

IF Sym-5 THEN PRINT "UC0.5.3.99.3.8.6.0.-3.-9:"

NEXT Xa

NEXT Xa
980
990
1009
1010
1020
        PRINT "PU"
1030
        BEEP
10.40
        ASSIGN #File 10 *
1050
        FND
```

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Thesis T7621 c.1

Torres Natural convection cooling of a 3 by 3 array of rectangular protrusions in an enclosure filled with dielectric liquid.

Thesis T7621

Torres c.1 Natural convection cooling of a 3 by 3 array of rectangular protrusions in an enclosure filled with dielectric liquid.



